

Freescale Semiconductor Data Sheet

Document Number: MSC7119 Rev. 8, 4/2008

MSC7119

Low-Cost 16-bit DSP with DDR Controller and 10/100 Mbps Ethernet MAC



- StarCore[®] SC1400 DSP extended core with one SC1400 DSP core, 256 Kbyte of internal SRAM M1 memory, 16 way 16 Kbyte instruction cache (ICache), four-entry write buffer, programmable interrupt controller (PIC), and low-power Wait and Stop processing modes.
- 192 Kbyte M2 memory for critical data and temporary data buffering.
- 8 Kbyte boot ROM.
- AHB-Lite crossbar switch that allows parallel data transfers
 between four master ports and six slave ports, where each port
 connects to an AHB-Lite bus; fixed or round robin priority
 programmable at each slave port; programmable bus parking at
 each slave port; low power mode.
- Internal PLL generates up to 300 MHz clock for the SC1400 core and up to 150 MHz for the crossbar switch, DMA channels, M2 memory, and other peripherals.
- Clock synthesis module provides predivision of PLL input clock; independent clocking of the internal timers and DDR module; programmable operation in the SC1400 low power Stop mode; independent shutdown of different regions of the device.
- Enhanced 16-bit wide host interface (HDI16) provides a glueless connection to industry-standard microcomputers, microprocessors, and DSPs and can also operate with an 8-bit host data bus, making if fully compatible with the DSP56300 HI08 from the external host side.
- DDR memory controller that supports byte enables for up to a 32-bit data bus; glueless interface to 150 MHz 14-bit page mode DDR-RAM; 14-bit external address bus supporting up to 1 Gbyte; and 16-bit or 32-bit external data bus.
- Programmable memory interface with independent read buffers, programmable predictive read feature for each buffer, and a write buffer.
- System control unit performs software watchdog timer function; includes programmable bus time-out monitors on AHB-Lite slave buses; includes bus error detection and programmable time-out monitors on AHB-Lite master buses; and has address out-of-range detection on each crossbar switch buses.
- Event port collects and counts important signal events including DMA and interrupt requests and trigger events such as interrupts, breakpoints, DMA transfers, or wake-up events; units operate independently, in sequence, or triggered externally; can be used standalone or with the OCE10.

- Multi-channel DMA controller with 32 time-multiplexed unidirectional channels, priority-based time-multiplexing between channels using 32 internal priority levels, fixed- or round-robin-priority operation, major-minor loop structure, and DONE or DRACK protocol from requesting units.
- Two independent TDM modules with independent receive and transmit, programmable sharing of frame sync and clock, programmable word size (8 or 16-bit), hardware-base A-law/μ-law conversion, up to 50 Mbps data rate per TDM, up to 128 channels, with glueless interface to E1/T1 frames and MVIP, SCAS, and H.110 buses.
- Ethernet controller with support for 10/100 Mbps MII/RMII designed to comply with IEEE Std. 802.3TM, 802.3uTM, 802.3uTM, and 802.3acTM; with internal receive and transmit FIFOs and a FIFO controller; direct access to internal memories via its own DMA controller; full and half duplex operation; programmable maximum frame length; virtual local area network (VLAN) tag and priority support; retransmission of transmit FIFO following collision; CRC generation and verification for inbound and outbound packets; and address recognition including promiscuous, broadcast, individual address. hash/exact match, and multicast hash match.
- UART with full-duplex operation up to 5.0 Mbps.
- Up to 41 general-purpose input/output (GPIO) ports.
- I²C interface that allows booting from EEPROM devices up to 1 Mbyte.
- Two quad timer modules, each with sixteen configurable 16-bit timers
- fieldBISTTM unit detects and provides visibility into unlikely field
 failures for systems with high availability to ensure structural
 integrity, that the device operates at the rated speed, is free from
 reliability defects, and reports diagnostics for partial or complete
 device inoperability.
- Standard JTAG interface allows easy integration to system firmware and internal on-chip emulation (OCE10) module.
- Optional booting external host via 8-bit or 16-bit access through the HDI16, 1²C, or SPI using in the boot ROM to access serial SPI Flash/EEPROM devices; different clocking options during boot with the PLL on or off using a variety of input frequency ranges.





Table of Contents

1	Pin As	signments4	Figure 8.	TDM Receive Signals	28
	1.1 N	MAP-BGA Ball Layout Diagrams	Figure 9.	TDM Transmit Signals	29
		Signal List By Ball Location	Figure 10.	Ethernet Receive Signal Timing	29
2		cal Characteristics	Figure 11.		
	2.1 N	Maximum Ratings	Figure 12.	Asynchronous Input Signal Timing	30
	2.2 F	Recommended Operating Conditions18	Figure 13.	Serial Management Channel Timing	31
		Thermal Characteristics	Figure 14.	Read Timing Diagram, Single Data Strobe	33
	2.4	DC Electrical Characteristics		Read Timing Diagram, Double Data Strobe	
	2.5 A	AC Timings	Figure 16.	Write Timing Diagram, Single Data Strobe	34
3		are Design Considerations41	Figure 17.	Write Timing Diagram, Double Data Strobe	34
	3.1	Thermal Design Considerations	Figure 18.	Host DMA Read Timing Diagram, HPCR[OAD] = 03	35
	3.2 F	Power Supply Design Considerations42	Figure 19.	Host DMA Write Timing Diagram, HPCR[OAD] = 0 3	35
		Estimated Power Usage Calculations49		I2C Timing Diagram	
	3.4 F	Reset and Boot	Figure 21.	UART Input Timing	37
	3.5	DDR Memory System Guidelines	Figure 22.	UART Output Timing	37
4	Orderin	ng Information57	Figure 23.	EE Pin Timing	37
5	Packag	ge Information58	Figure 24.	EVNT Pin Timing	38
6		ct Documentation	Figure 25.		
7	Revision	on History	Figure 26.	Test Clock Input Timing Diagram	39
	-4 -4 F	"	Figure 27.	Boundary Scan (JTAG) Timing Diagram	40
		igures	Figure 28.	Test Access Port Timing Diagram	40
Fig	jure 1.	MSC7119 Block Diagram	Figure 29.	TRST Timing Diagram	40
Fig	ure 2.	MSC7119 Molded Array Process-Ball Grid Array	Figure 30.	Voltage Sequencing Case 1	43
		(MAP-BGA), Top View 4	Figure 31.	Voltage Sequencing Case 2	44
Fig	jure 3.	MSC7119 Molded Array Process-Ball Grid Array	Figure 32.	Voltage Sequencing Case 3	45
		(MAP-BGA), Bottom View 5	Figure 33.	Voltage Sequencing Case 4	46
_	jure 4.	Timing Diagram for a Reset Configuration Write 25	Figure 34.	Voltage Sequencing Case 5	47
_	jure 5.	DDR DRAM Input Timing Diagram 26	Figure 35.	PLL Power Supply Filter Circuits	48
_	jure 6.	DDR DRAM Output Timing Diagram 27	Figure 36.	SSTL Termination Techniques	54
Fig	jure 7.	DDR DRAM AC Test Load	Figure 37.	SSTI Power Value	55



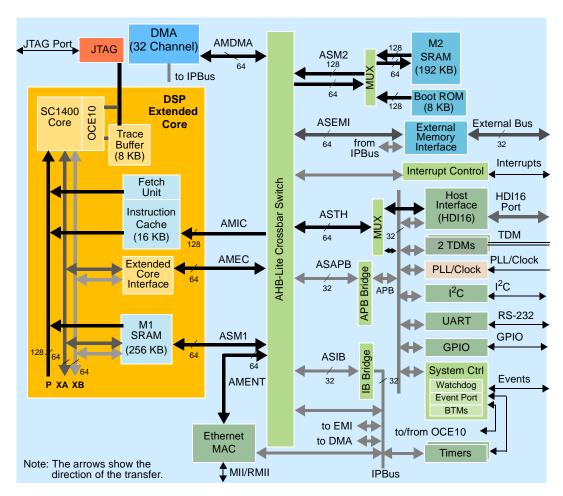


Figure 1. MSC7119 Block Diagram



1 Pin Assignments

This section includes diagrams of the MSC7119 package ball grid array layouts and pinout allocation tables.

1.1 MAP-BGA Ball Layout Diagrams

Top and bottom views of the MAP-BGA package are shown in Figure 2 and Figure 3 with their ball location index numbers.

Top View 1 2 3 5 6 8 10 12 13 14 15 16 17 18 19 20 4 11 GND DQM1 DQS2 CK HD15 HD12 HD10 GND HD7 HD6 HD4 HD1 HD0 GND вмз NC NC CS0 DQM2 DQS3 DQS0 WE HD14 HD11 NC В V_{DDM} DQS1 D30 D25 CS1 DQM3 DQM0 RAS CAS HD13 HD9 HD3 NC NC C GND D28 D27 V_{DDM} V_{DDM} V_{DDM} V_{DDM} NC V_{DDM} V_{DDM} V_{DDIO} V_{DDIC} V_{DDIO} V_{DDIO} V_{DDIC} V_{DDIC} D Е V_{DDM} V_{DDM} V_{DDC} V_{DDC} V_{DDC} V_{DDC} V_{DDM} V_{DDIO} V_{DDIC} V_{DDIO} V_{DDIO} V_{DDIO} V_{DDC} V_{DDC} NC V_{DDC} D15 D29 V_{DDC} V_{DDC} GND GND GND GND GND GND V_{DDC} NC V_{DDM} V_{DDM} V_{DDIC} F GND D13 NC G GND GND GND GND GND GND GND GND GND D12 D11 V_{DDM} V_{DDIO} V_{DDIO} HA1 Н V_{DDM} V_{DDM} GND GND GND GND GND GND GND GND HREQ V_{DDM} V_{DDM} V_{DDIO} V_{DDC} HA3 GND HDS V_{DDC} V_{DDM} V_{DDIO} V_{DDIO} V_{DDC} HA0 HDDS Κ GND GND GND GND GND GND GND GND GND HCS2 HCS' HRW V_{DDC} V_{DDM} V_{DDIO} V_{DDIO} V_{DDIO} GND GND URXD V_{DDM} V_{DDM} V_{DDM} V_{DDC} V_{DDC} GND GND GND GND GND GND GND GND CLKIN V_{DDM} V_{DDM} V_{DDM} V_{DDIO} V_{DDC} Ν V_{SSPL} ORESE D17 D16 V_{DDM} V_{DDM} GND GND GND GND GND GND GND GND V_{DDIO} V_{DDIO} TPSE V_{DDPL} TESTO R V_{DDM} V_{DDM} V_{DDM} V_{DDM} V_{DDM} V_{DDIO} V_{DDIO} V_{DDIO} D20 D22 V_{DDM} V_{DDM} V_{DDC} V_{DDM} V_{DDM} V_{DDC} V_{DDM} V_{DDM} V_{DDIO} V_{DDIO} V_{DDIO} V_{DDIO} V_{DDC} V_{DDC} MDIO TMS HRESET TRST D21 D23 V_{DDC} COL TCK U EVNT4 TOTCK T1RFS TX_ER EVNT1 EVNT2 TORFS TOTFS T1RD T1TFS TXD2 RXD3 TXD1 TXCLK RX_EF GND MDC W V_{DDM} EVNT3 T0RCk T0RD TOTD . T1RCk RXD1 GND TXD3 RXCL GND RX_D\

Figure 2. MSC7119 Molded Array Process-Ball Grid Array (MAP-BGA), Top View



Bottom View 7 20 19 18 17 16 15 14 13 12 11 10 9 8 6 5 4 3 2 1 CK GND BM2 HD2 HD5 HD8 HD11 HD14 CKE DQS0 DQS3 DQM2 V_{DDM} В NC DQS1 DQM0 DQM3 HD3 HD9 HD13 RAS CS1 D24 GND V_{DDIO} V_{DDIO} V_{DDIO} V_{DDIO} V_{DDIO} V_{DDIO} V_{DDM} V_{DDM} V_{DDM} V_{DDM} V_{DDM} V_{DDM} V_{DDM} V_{DD} V_{DD} V_{DDIO} V_{DDIO} V_{DDM} V_{DD} V_{DD} V_{DD} V_{DD} V_{DDM} V_{DDM} GND F V_{DDIO} V_{DDIO} V_{DDIO} GND GND GND GND V_{DDIO} GND GND D29 D15 V_{DDM} GND V_{DDIO} V_{DDIO} GND GND GND GND GND V_{DDM} V_{DDM} GND G GND GND GND GND GND GND GND D14 Н V_{DDM} HACK НАЗ GND GND GND GND GND GND GND GND GND HREQ V_{DDIO} V_{DDM} V_{DDM} V_{DDM} V_{DDM} D10 HDDS GND GND GND GND GND GND HA0 V_{DDIO} V_{DDIO} GND GND GND V_{DDM} GND HCS1 HCS2 GND GND GND GND GND GND GND GND D1 V_{DD} V_{DDIO} V_{DDIO} V_{DDIO} V_{DDM} V_{DD} L UTXD GND GND URXD SDA GND GND GND GND GND GND GND GND V_{DDM} V_{DDM} D2 М GND GND CLKIN GND GND GND GND GND D4 GND Ν V_{SSPLL} V_{DDIO} V_{DDM} V_{DDM} V_{DDM} PORESE V_{DD} GND GND GND GND GND GND D7 Р V_{DDIO} V_{DDIO} V_{DDM} V_{DDM} V_{DDM} V_{DDPLL} GND GND TEST0 EE0 TDO V_{DDIO} V_{DDIO} GND V_{DDIO} GND V_{DDM} V_{DDM} GND V_{DDM} V_{DDM} D18 D19 GND R V_{DDM} TMS MDIO D22 D20 V_{DDM} Т V_{DDIO} V_{DDIO} V_{DDIO} TCK COL V_{DD} V_{DDM} GND TX_EN RXD0 RXD2 TX_ER T1TD T1RFS TOTCK , EVNT4 EVNTO BA0 A10 A11 A13 V_{DDM} RX_ER TORFS RXD3 TXD2 T1TFS , T1RD T0TFS EVNT2 EVNT1 Α8 A12 GND W

Figure 3. MSC7119 Molded Array Process-Ball Grid Array (MAP-BGA), Bottom View

T0RD

TXD3

RX_D\

T1RCK

TOTD



1.2 Signal List By Ball Location

Table 1 lists the signals sorted by ball number and configuration.

Table 1. MSC7119 Signals by Ball Designator

	Signal Names									
Number		S	oftware Controlle	ed	Hardware	Controlled				
	End of Reset	GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate				
A1		GND								
A2			G	ND						
А3			DC	QM1						
A4			DC	QS2						
A5			C	CK						
A6			C	K						
A7		GPIC7		GPOC7	Н	D15				
A8		GPIC4		GPOC4	Н	012				
A9		GPIC2		GPOC2	Н	D10				
A10		rese	rved		Н	D7				
A11		rese	rved		HD6					
A12		rese	rved		D4					
A13		rese	rved		Н	D1				
A14		rese	rved		Н	D0				
A15			G	ND						
A16	ВМ3	GP	ID8	GPOD8	rese	erved				
A17			N	IC						
A18			N	IC						
A19			N	IC						
A20			N	IC						
B1			V _E	DDM						
B2			N	IC						
В3			C	S 0						
B4			DC	QM2						
B5			DC	QS3						
В6			DC	QS0						
В7			С	KE						
B8			V	/E						
В9		GPIC6		GPOC6	Н	014				
B10		GPIC3		GPOC3	Н	D11				
B11		GPIC0		GPOC0	Н	D8				
B12		rese	rved		Н	D5				
B13		rese	rved		Н	D2				



	Signal Names									
Number		Software Controlled			Hardware Controlled					
	End of Reset	GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate				
B14			1	IC		•				
B15	BM2	GPI	ID7	GPOD7	rese	erved				
B16			١	IC						
B17			١	IC						
B18			١	IC						
B19			١	IC						
B20			1	IC						
C1			С	024						
C2				30						
C3			С	25						
C4			Ō	S1						
C5			DO	QM3						
C6			DO	QMO						
C7			DO	QS1						
C8			R	AS						
C9			C	AS						
C10		GPIC5		GPOC5	HI	D13				
C11		GPIC1		GPOC1	HD9					
C12		rese	rved		Н	D3				
C13			1	1C						
C14			1	1C						
C15			1	1C						
C16			1	IC						
C17			1	IC						
C18			1	IC						
C19			1	IC						
C20			1	IC						
D1			VI	DDM						
D2				228						
D3			D	27						
D4			G	ND						
D5			VI	DDM						
D6				DDM						
D7				DDM						
D8				DDM						
D9				DDM						



	Signal Names									
Number		So	Software Controlled			Hardware Controlled				
	End of Reset	GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate				
D10		V_DDM								
D11		V _{DDIO}								
D12										
D13			V _C	ODIO						
D14			V _C	ODIO						
D15			V _C	DIO						
D16			V _C	DIO						
D17			V _E	DDC						
D18				IC						
D19			N	IC						
D20			N	IC						
E1			G	ND						
E2			D	26						
E3			D	31						
E4			V _E	DDM						
E5				DDM						
E6				DDC						
E7				DDC						
E8				DDC						
E9				DDC						
E10				DDM						
E11				DDIO						
E12				ODIO						
E13				ODIO						
E14				DDIO						
E15				DDIO						
E16				DDC						
E17				DDC						
E18				IC						
E19			N	IC						
E20			N	IC						
F1			V _E	DDM						
F2				15						
F3			D	29						
F4			V _[DDC						
F5				DDC						



	Signal Names									
Number		Sc	Software Controlled			Controlled				
	End of Reset	GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate				
F6		V _{DDC}								
F7		GND								
F8		GND								
F9			G	ND						
F10			V _I	DDM						
F11			V _I	DDM						
F12			G	ND						
F13			G	ND						
F14			G	ND						
F15			V _[DDIO						
F16				DDC						
F17				DDC						
F18				1C						
F19			N	IC .						
F20			N	IC						
G1			G	ND						
G2			D	013						
G3			G	ND						
G4			V _[DDM						
G5				DDM						
G6				ND						
G7			G	ND						
G8			G	ND						
G9			G	ND						
G10			G	ND						
G11			G	ND						
G12			G	ND						
G13			G	ND						
G14			G	ND						
G15			V _E	DDIO						
G16				DDIO						
G17				DDC						
G18				NC						
G19				IC .						
G20				IC .						
H1				014						



	Signal Names									
Number		S	Software Controlled			Controlled				
	End of Reset	GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate				
H2		D12								
НЗ		D11								
H4		V_DDM								
H5			V _D	DM						
H6			GI	ND						
H7			GI	ND						
H8			GI	ND						
H9			GI	ND						
H10			GI	ND						
H11			GI	ND						
H12			GI	ND						
H13			GI	ND						
H14			GI	ND						
H15			V _D	DIO						
H16				DIO						
H17				DDC						
H18				С						
H19		rese	rved		Н	IA2				
H20		rese	rved		Н	IA1				
J1			D	10						
J2			V _D	DM						
J3				9						
J4			V _D	DM						
J5				DM						
J6				DM						
J7				ND						
J8			GI	ND						
J9			GI	ND						
J10			GI	ND						
J11			GI	ND						
J12			GI	ND						
J13			GI	ND						
J14			GI	ND						
J15			GI	ND						
J16			V _D	DIO						
J17				DDC						



	Signal Names									
Number		S	oftware Controll	ed	Hardware	Controlled				
	End of Reset	GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate				
J18		GPIC11		GPOC11	Н	A3				
J19		rese	rved		HACK/HACK or HRRQ/HRRQ					
J20	HDSP		reserved		HREQ/HREQ	or HTRQ/HTRQ				
K1		D0								
K2			G	ND						
K3				D8						
K4			V	DDC						
K5				DDM						
K6				ND						
K7			G	ND						
K8			G	ND						
K9			G	ND						
K10			G	ND						
K11			G	ND						
K12			G	ND						
K13			G	ND						
K14			G	ND						
K15			V	DDIO						
K16				DDIO						
K17				DDC						
K18		rese			Н	A0				
K19		rese	rved		HD	DDS				
K20		rese	rved		HDS/HDS o	or HWR/HWR				
L1				 D1						
L2			G	ND						
L3				D3						
L4			V	DDC						
L5				DDM						
L6				ND						
L7			G	ND						
L8			G	ND						
L9			G	ND						
L10			G	ND						
L11			G	ND						
L12			G	ND						
L13			G	ND						

MSC7119 Data Sheet, Rev. 8



	Signal Names									
Number		Software Controlled			Hardware	Controlled				
	End of Reset	GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate				
L14										
L15			ODIO							
L16			V	ODIO						
L17			V	DDC						
L18		GPIB11		GPOB11	HCS2	P/HCS2				
L19		rese	rved		HCS1	/HCS1				
L20		rese	rved		HRW or	HRD/HRD				
M1				D2						
M2			V	DDM						
М3				D5						
M4			V	DDM						
M5			V	DDM						
M6				IND						
M7			G	ND						
M8			G	ND						
M9			G	IND						
M10			G	IND						
M11			G	ND						
M12			G	ND						
M13			G	IND						
M14			G	ND						
M15			G	ND						
M16			V	DDC						
M17			V	DDC						
M18	GPI	A14	ĪRQ15	GPOA14	S	DA				
M19	GPI	A12	ĪRQ3	GPOA12	U	ΓXD				
M20	GPI	A13	ĪRQ2	GPOA13	UF	RXD				
N1				D4						
N2				D6						
N3			V	REF						
N4			V	DDM						
N5			V	DDM						
N6				DDM						
N7			G	iND						
N8			G	iND						
N9			G	iND						



	Signal Names									
Number		Software Controlled			Hardware Controlled					
	End of Reset	GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate				
N10		GND								
N11			G	ND						
N12			G	ND						
N13			G	ND						
N14			G	ND						
N15			V _D	DIO						
N16			V _E	DC						
N17			V _E	DDC						
N18				KIN						
N19	GPI	A15	ĪRQ14	GPOA15	S	CL				
N20			V _S	SPLL						
P1				7						
P2			D	17						
P3			D	16						
P4			V _D	DM						
P5				DM						
P6				DM						
P7				ND						
P8			G	ND						
P9			G	ND						
P10			G	ND						
P11			G	ND						
P12			G	ND						
P13			G	ND						
P14			G	ND						
P15			V _D	DIO						
P16				DIO						
P17				DDC						
P18				ESET						
P19			TP	SEL						
P20			V _{DI}	PLL						
R1				ND						
R2			D	19						
R3			D	18						
R4			V _C	DM						
R5				DM						



	Signal Names									
Number		S	oftware Controlle	ed	Hardware	Controlled				
	End of Reset	GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate				
R6			V _C	DDM		·				
R7		GND								
R8		V_{DDM}								
R9			G	ND						
R10			V _C	DDM						
R11				ND						
R12			G	ND						
R13			V _D	DDIO						
R14				ND						
R15			V _D	DDIO						
R16				DDIO						
R17				DDC						
R18										
R19		rese	rved		EE0/[DBREQ				
R20			TE	ST0						
T1			V _D	DDM						
T2				20						
Т3			D	22						
T4			V _D	DDM						
T5			V _D	DDM						
T6				DDC						
T7				DDM						
T8				DDM						
Т9				DDC						
T10				DDM						
T11				DDM						
T12				DDIO						
T13				DDIO						
T14				DDIO						
T15				DIDIO						
T16				DDC						
T17				DDC						
T18		rese	erved		М	DIO				
T19			TI	MS						
T20			HRE	SET						
U1			G	ND						



Number		S	oftware Controlle	ed	Hardware (Controlled			
	End of Reset	GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate			
U2		D21							
U3			D	23					
U4			V_{D}	DDM					
U5			V _D	DDC					
U6			V _D	DDC					
U7			V _D	DDC					
U8			V _D	DDC					
U9			V _D	DDC					
U10			V _C	DDC					
U11			V _C	DDC					
U12			V _C	DDC					
U13			V _C	DDC					
U14			V _C	DDC					
U15			V _C	DDC					
U16			V _D	DDC					
U17				DDC					
U18		rese	rved		CC)L			
U19			TO	CK					
U20			TR	ST					
V1			V _D	DDM					
V2				IC					
V3			A	13					
V4			A	11					
V5			A	10					
V6			Д	1.5					
V7			Д	Λ2					
V8			В	A0					
V9			N	IC					
V10		rese	rved		EVN	ITO			
V11	SWTE	GPIA16	ĪRQ12	GPOA16	EVN	IT4			
V12	GP	IA8	IRQ6	GPOA8	TOTCK				
V13	GP	IA4	ĪRQ1	GPOA4	T1RFS				
V14	GP		ĪRQ11	GPOA0	T1TD				
V15	GPI	A28	ĪRQ17	GPOA28	TX_ER	reserved			
V16		GPID6		GPOD6	RXD2	reserved			
V17	GPI	A22	ĪRQ22	GPOA22	RX				



Table 1. MSC7119 Signals by Ball Designator (continued)

	Signal Names								
Number		S	oftware Control	ed	Hardware Controlled				
	End of Reset	GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate			
V18	GPIA24 IRQ24 GPOA24 TX_E					_EN			
V19		rese	rved		CI	RS			
V20			-	TDI					
W1			C	SND					
W2			V	DDM					
W3			,	A12					
W4				A8					
W5				A7					
W6				A6					
W7				A3					
W8				NC					
W9	GPI	A17	ĪRQ13	GPOA17	EVNT1	CLKO			
W10	ВМО	GPI	C14	GPOC14	EVI	NT2			
W11	GPI	A10	ĪRQ5	GPOA10	TOF	RFS			
W12	GP	IA7	ĪRQ7	GPOA7	T0TFS				
W13	GP	IA3	ĪRQ8	GPOA3	T1	RD			
W14	GP	IA1	ĪRQ10	GPOA1	T1TFS				
W15		GPID4		GPOD4	TXD2 reserve				
W16	GPI	A27	ĪRQ18	GPOA27	RXD3	reserved			
W17	GPI	A19	ĪRQ19	GPOA19	TX				
W18	GPI	A23	ĪRQ23	GPOA23	TXCLK or REFCLK				
W19	GPI	A26	ĪRQ26	GPOA26	RX_ER				
W20	H8BIT		reserved		MI	DC			
Y1			V	DDM					
Y2				SND					
Y3				A9					
Y4				A1					
Y5				A0					
Y6				A4					
Y7			E	BA1					
Y8	rese	rved	NMI		reserved				
Y9	BM1	GPI	C15	GPOC15	EVNT3				
Y10	GPI	A11	ĪRQ4	GPOA11	TOF	RCK			
Y11		GPIA9		GPOA9	T0	RD			
Y12		GPIA6		GPOA6	TOTD				
Y13	GP	IA5	ĪRQ0	GPOA5	T1RCK				



Table 1. MSC7119 Signals by Ball Designator (continued)

	Signal Names					
Number		s	Software Controlled			Controlled
	End of Reset	GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
Y14	GPIA2		ĪRQ9	GPOA2	T1TCK	
Y15	GPIA29		ĪRQ16	GPOA29	TXD3	reserved
Y16	GPID5			GPOD5	RXCLK	reserved
Y17	GPIA20		ĪRQ20	GPOA20	TX	(D0
Y18	GPIA21		ĪRQ21	GPOA21	RXD1	
Y19	,			ND		
Y20	GPI	A25	ĪRQ25	GPOA25	RX_DV o	r CRS_DV

2 Electrical Characteristics

This document contains detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications. For additional information, see the *MSC711x Reference Manual*.

2.1 Maximum Ratings

CAUTION

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, normal precautions should be taken to avoid exceeding maximum voltage ratings. Reliability is enhanced if unused inputs are tied to an appropriate logic voltage level (for example, either GND or V_{DD}).

In calculating timing requirements, adding a maximum value of one specification to a minimum value of another specification does not yield a reasonable sum. A maximum specification is calculated using a worst case variation of process parameter values in one direction. The minimum specification is calculated using the worst case for the same parameters in the opposite direction. Therefore, a "maximum" value for a specification never occurs in the same device with a "minimum" value for another specification; adding a maximum to a minimum represents a condition that can never exist.



rical Characteristics

Table 2 describes the maximum electrical ratings for the MSC7119.

Table 2. Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Core supply voltage	V _{DDC}	1.5	V
Memory supply voltage	V_{DDM}	4.0	V
PLL supply voltage	V _{DDPLL}	1.5	V
I/O supply voltage	V_{DDIO}	-0.2 to 4.0	V
Input voltage	V _{IN}	(GND – 0.2) to 4.0	V
Reference voltage	V _{REF}	4.0	V
Maximum operating temperature	TJ	105	°C
Minimum operating temperature	T _A	-40	°C
Storage temperature range	T _{STG}	-55 to +150	°C

Notes:

- 1. Functional operating conditions are given in Table 3.
- 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximum is not guaranteed. Stress beyond the listed limits may affect device reliability or cause permanent damage.
- 3. Section 3.1, Thermal Design Considerations includes a formula for computing the chip junction temperature (T_J).

2.2 Recommended Operating Conditions

Table 3 lists recommended operating conditions. Proper device operation outside of these conditions is not guaranteed.

Table 3. Recommended Operating Conditions

Rating	Symbol	Value	Unit
Core supply voltage	V _{DDC}	1.14 to 1.26	V
Memory supply voltage	V_{DDM}	2.38 to 2.63	V
PLL supply voltage	V _{DDPLL}	1.14 to 1.26	V
I/O supply voltage	V _{DDIO}	3.14 to 3.47	V
Reference voltage	V _{REF}	1.19 to 1.31	V
Operating temperature range	T _J T _A	maximum: 105 minimum: –40	°C °C

19



2.3 Thermal Characteristics

Table 4 describes thermal characteristics of the MSC7119 for the MAP-BGA package.

Table 4. Thermal Characteristics for MAP-BGA Package

		MAP-BGA		
Characteristic	Symbol	Natural Convection	200 ft/min (1 m/s) airflow	Unit
Junction-to-ambient ^{1, 2}	$R_{ heta JA}$	39	31	°C/W
Junction-to-ambient, four-layer board ^{1, 3}	$R_{ hetaJA}$	23	20	°C/W
Junction-to-board ⁴	$R_{ heta JB}$	12		°C/W
Junction-to-case ⁵	$R_{ heta JC}$	7		°C/W
Junction-to-package-top ⁶	Ψ_{JT}	2		°C/W

Notes:

- Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
- 2. Per SEMI G38-87 and JEDEC JESD51-2 with the single layer board horizontal.
- 3. Per JEDEC JESD51-6 with the board horizontal.
- 4. Thermal resistance between the die and the printed circuit board per JEDEC JESD 51-8. Board temperature is measured on the top surface of the board near the package.
- 5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
- **6.** Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2.

Section 3.1, Thermal Design Considerations explains these characteristics in detail.

2.4 DC Electrical Characteristics

This section describes the DC electrical characteristics for the MSC7119.

Note: The leakage current is measured for nominal voltage values must vary in the same direction (for example, both V_{DDIO} and V_{DDC} vary by +2 percent or both vary by -2 percent).

Table 5. DC Electrical Characteristics

Characteristic	Symbol	Min	Typical	Max	Unit
Core and PLL voltage	V _{DDC} V _{DDPLL}	1.14	1.2	1.26	V
DRAM interface I/O voltage ¹	V_{DDM}	2.375	2.5	2.625	V
I/O voltage	V_{DDIO}	3.135	3.3	3.465	V
DRAM interface I/O reference voltage ²	V _{REF}	$0.49 \times V_{DDM}$	1.25	$0.51 \times V_{DDM}$	V
DRAM interface I/O termination voltage ³	VTT	V _{REF} – 0.04	V_{REF}	V _{REF} + 0.04	V
Input high CLKIN voltage	V _{IHCLK}	2.4	3.0	3.465	V
DRAM interface input high I/O voltage	V _{IHM}	V _{REF} + 0.28	V_{DDM}	V _{DDM} + 0.3	V
DRAM interface input low I/O voltage	V _{ILM}	-0.3	GND	V _{REF} – 0.18	V
Input leakage current, V _{IN} = V _{DDIO}	I _{IN}	-1.0	0.09	1	μΑ
V _{REF} input leakage current	I _{VREF}	_	_	5	μΑ

MSC7119 Data Sheet, Rev. 8



rical Characteristics

Table 5. DC Electrical Characteristics (continued)

Characteristic	Symbol	Min	Typical	Max	Unit
Tri-state (high impedance off state) leakage current, V _{IN} = V _{DDIO}	I _{OZ}	-1.0	0.09	1	μA
Signal low input current, V _{IL} = 0.4 V	ΙL	-1.0	0.09	1	μA
Signal high input current, V _{IH} = 2.0 V	I _H	-1.0	0.09	1	μA
Output high voltage, I _{OH} = -2 mA, except open drain pins	V _{OH}	2.0	3.0	_	V
Output low voltage, I _{OL} = 5 mA	V _{OL}	_	0	0.4	V
Typical power at 300 MHz ⁵	Р	_	324.0	_	mW

Notes: 1. The value of V_{DDM} at the MSC7119 device must remain within 50 mV of V_{DDM} at the DRAM device at all times.

- V_{REF} must be equal to 50% of V_{DDM} and track V_{DDM} variations as measured at the receiver. Peak-to-peak noise must not exceed ±2% of the DC value.
- V_{TT} is not applied directly to the MSC7119 device. It is the level measured at the far end signal termination. It should be equal
 to V_{REF}. This rail should track variations in the DC level of V_{REF}.
- Output leakage for the memory interface is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ V_{DDM}.
- 5. The core power values were measured.using a standard EFR pattern at typical conditions (25°C, 300 MHz, 1.2 V core).

Table 6 lists the DDR DRAM capacitance.

Table 6. DDR DRAM Capacitance

Parameter/Condition	Symbol	Max	Unit
Input/output capacitance: DQ, DQS	C _{IO}	30	pF
Delta input/output capacitance: DQ, DQS	C _{DIO}	30	pF

Note: These values were measured under the following conditions:

- $V_{DDM} = 2.5 V \pm 0.125 V$
- f = 1 MHz
- T_A = 25°C
- $V_{OUT} = V_{DDM}/2$
- V_{OUT} (peak to peak) = 0.2 V



2.5 AC Timings

This section presents timing diagrams and specifications for individual signals and parallel I/O outputs and inputs. All AC timings are based on a 30 pF load, except where noted otherwise, and a 50 Ω transmission line. For any additional pF, use the following equations to compute the delay:

Standard interface: 2.45 + (0.054 × C_{load}) ns
 DDR interface: 1.6 + (0.002 × C_{load}) ns

2.5.1 Clock and Timing Signals

The following tables describe clock signal characteristics. **Table 6** shows the maximum frequency values for internal (core, reference, and peripherals) and external (CLKO) clocks. You must ensure that maximum frequency values are not exceeded (see **Section 2.5.2** for the allowable ranges when using the PLL).

Table 6. Maximum Frequencies

Characteristic	Maximum in MHz
Core clock frequency (CLOCK)	300
External output clock frequency (CLKO)	75
Memory clock frequency (CK, CK)	150
TDM clock frequency (TxRCK, TxTCK)	50

Table 7. Clock Frequencies in MHz

Characteristic	Symbol	Min	Max
CLKIN frequency	F _{CLKIN}	10	100
CLOCK frequency	F _{CORE}	_	300
CK, CK frequency	F _{CK}	_	150
TDMxRCK, TDMxTCK frequency	F _{TDMCK}		50
CLKO frequency	F _{CKO}	_	75
AHB/IPBus/APB clock frequency	F _{BCK}	_	150
Note: The rise and fall time of external clocks should be 5 ns ma	ximum		

Table 8. System Clock Parameters

Characteristic	Min	Max	Unit
CLKIN frequency	10	100	MHz
CLKIN slope	_	5	ns
CLKIN frequency jitter (peak-to-peak)	_	1000	ps
CLKO frequency jitter (peak-to-peak)	_	150	ps

MSC7119 Data Sheet, Rev. 8

Freescale Semiconductor

21

2.5.2 Configuring Clock Frequencies

This section describes important requirements for configuring clock frequencies in the MSC7119 device when using the PLL block. To configure the device clocking, you must program four fields in the Clock Control Register (CLKCTL):

- *PLLDVF field*. Specifies the PLL division factor (PLLDVF + 1) to divide the input clock frequency F_{CLKIN}. The output of the divider block is the input to the multiplier block.
- *PLLMLTF field.* Specifies the PLL multiplication factor (PLLMLTF + 1). The output from the multiplier block is the loop frequency F_{LOOP}.
- RNG field. Selects the available PLL frequency range for F_{VCO}, either F_{LOOP} when the RNG bit is set (1) or F_{LOOP}/2 when the RNG bit is cleared (0).
- CKSEL field. Selects F_{CLKIN} , F_{VCO} , or $F_{VCO}/2$ as the source for the core clock.

There are restrictions on the frequency range permitted at the beginning of the multiplication portion of the PLL that affect the allowable values for the PLLDVF and PLLMLTF fields. The following sections define these restrictions and provide guidelines to configure the device clocking when using the PLL. Refer to the Clock and Power Management chapter in the *MSC711x Reference Manual* for details on the clock programming model.

2.5.2.1 PLL Multiplier Restrictions

There are two restrictions for correct usage of the PLL block:

- The input frequency to the PLL multiplier block (that is, the output of the divider) must be in the range 10–25 MHz.
- The output frequency of the PLL multiplier must be in the range 266–532 MHz.

When programming the PLL for a desired output frequency using the PLLDVF, PLLMLTF, and RNG fields, you must meet these constraints.

2.5.2.2 Input Division Factors and Corresponding CLKIN Frequency Range

The value of the PLLDVF field determines the allowable CLKIN frequency range, as shown in **Table 9**.

Table 9. CLKIN Frequency Ranges by Divide Factor Value

	Factor	CLKIN Frequency Range	Comments
0x00	1	10 to 25 MHz	Input Division by 1
0x01	2	20 to 50 MHz	Input Division by 2
0x02	3	30 to 75 MHz	Input Division by 3
0x03	4	40 to 100 MHz	Input Division by 4
0x04	5	50 to 100 MHz	Input Division by 5
0x05	6	60 to 100 MHz	Input Division by 6
0x06	7	70 to 100 MHz	Input Division by 7
0x07	8	80 to 100 MHz	Input Division by 8
0x08	9	90 to 100 MHz	Input Division by 9
0x09	10	100 MHz	Input Division by 10



2.5.2.3 Multiplication Factor Range

The multiplier block output frequency ranges depend on the divided input clock frequency as shown in Table 10.

Table 10. PLLMLTF Ranges

	Multiplier Block (Loop) Output Range	Minimum PLLMLTF Value	Maximum PLLMLTF Value
	266 ≤ [Divided Input Clock × (PLLMLTF + 1)] ≤ 532 MHz	266/Divided Input Clock	532/Divided Input Clock
Note	 This table results from the allowed range for F_{Loop}. The minim frequency of the Divided Input Clock. 	um and maximum multiplication fa	ctors are dependent on the

2.5.2.4 Allowed Core Clock Frequency Range

The frequency delivered to the core, extended core, and peripherals depends on the value of the CLKCTRL[RNG] bit as shown in **Table 11**.

Table 11. F_{vco} Frequency Ranges

CLI	KCTRL[RNG] Value	Allowed Range of F _{vco}
	1	266 ≤ F _{vco} ≤ 532 MHz
	0	133 ≤ F _{vco} ≤ 266 MHz
Note:	This table results from the	allowed range for F _{vco} , which is F _{Loop} modified by CLKCTRL[RNG].

This bit along with the CKSEL determines the frequency range of the core clock.

Table 12. Resulting Ranges Permitted for the Core Clock

CLKCTRL[CKSEL]	CLKCTRL[RNG]	Resulting Division Factor	Allowed Range of Core Clock	Comments
11	1	1	266 ≤ core clock ≤ 300 MHz	Limited by maximum core frequency
11	0	2	133 ≤ core clock ≤ 266 MHz	Limited by range of PLL
01	1	2	133 ≤ core clock ≤ 266 MHz	Limited by range of PLL
01	0	4	66.5 ≤ core clock ≤ 133 MHz	Limited by range of PLL
Note: This table res	ults from the allowed ran	ge for F _{OUT} , wh	ich depends on clock selected via CLKC	CTRL[CKSEL].

2.5.2.5 Core Clock Frequency Range When Using DDR Memory

The core clock can also be limited by the frequency range of the DDR devices in the system. **Table 13** summarizes this restriction.

Table 13. Core Clock Ranges When Using DDR

DDR Type	Allowed Frequency Range for DDR CK	Corresponding Range for the Core Clock	Comments
DDR 200 (PC-1600)	83–100 MHz	166 ≤ core clock ≤ 200 MHz	Core limited to 2 × maximum DDR frequency
DDR 266 (PC-2100)	83–133 MHz	166 ≤ core clock ≤ 266 MHz	Core limited to 2 × maximum DDR frequency
DDR 333 (PC-2600)	83–150 MHz	166 ≤ core clock ≤ 300 MHz	Core limited to 2 × maximum DDR frequency

2.5.3 Reset Timing

The MSC7119 device has several inputs to the reset logic. All MSC7119 reset sources are fed into the reset controller, which takes different actions depending on the source of the reset. The reset status register indicates the most recent sources to cause a reset. **Table 14** describes the reset sources.

Table 14. Reset Sources

Name	Direction	Description
Power-on reset (PORESET)	Input	Initiates the power-on reset flow that resets the MSC7119 and configures various attributes of the MSC7119. On PORESET, the entire MSC7119 device is reset. SPLL and DLL states are reset, HRESET is driven, the SC1400 extended core is reset, and system configuration is sampled. The system is configured only when PORESET is asserted.
External Hard reset (HRESET)	Input/ Output	Initiates the hard reset flow that configures various attributes of the MSC7119. While HRESET is asserted, HRESET is an open-drain output. Upon hard reset, HRESET is driven and the SC1400 extended core is reset.
Software watchdog reset	Internal	When the MSC7119 watchdog count reaches zero, a software watchdog reset is signalled. The enabled software watchdog event then generates an internal hard reset sequence.
Bus monitor reset	Internal	When the MSC7119 bus monitor count reaches zero, a bus monitor hard reset is asserted. The enabled bus monitor event then generates an internal hard reset sequence.
JTAG EXTEST, CLAMP, or HIGHZ command	Internal	When a Test Access Port (TAP) executes an EXTEST, CLAMP, or HIGHZ command, the TAP logic asserts an internal reset signal that generates an internal soft reset sequence.

Table 15 summarizes the reset actions that occur as a result of the different reset sources.

Table 15. Reset Actions for Each Reset Source

	Power-On Reset (PORESET)	H <u>ard Rese</u> t (HRESET)	S <u>oft Rese</u> t (SRESET)
Reset Action/Reset Source	External only	External or Internal (Software Watchdog or Bus Monitor)	JTAG Command: EXTEST, CLAMP, or HIGHZ
Configuration pins sampled (refer to Section 2.5.3.1 for details).	Yes	No	No
PLL and clock synthesis states Reset	Yes	No	No
HRESET Driven	Yes	Yes	No
Software watchdog and bus time-out monitor registers	Yes	Yes	Yes
Clock synthesis modules (STOPCTRL, HLTREQ, and HLTACK) reset	Yes	Yes	Yes
Extended core reset	Yes	Yes	Yes
Peripheral modules reset	Yes	Yes	Yes

2.5.3.1 Power-On Reset (PORESET) Pin

Asserting $\overline{\text{PORESET}}$ initiates the power-on reset flow. $\overline{\text{PORESET}}$ must be asserted externally for at least 16 CLKIN cycles after external power to the MSC7119 reaches at least 2/3 V_{DD}.



2.5.3.2 Reset Configuration

The MSC7119 has two mechanisms for writing the reset configuration:

- From a host through the host interface (HDI16)
- From memory through the I²C interface

Five signal levels (see **Chapter 1** for signal description details) are sampled on PORESET deassertion to define the boot and operating conditions:

- BM[0–1]
- SWTE
- H8BIT
- HDSP

2.5.3.3 Reset Timing Tables

Table 16 and Figure 4 describe the reset timing for a reset configuration write.

Table 16. Timing for a Reset Configuration Write

No.	Characteristics	Expression	Unit
1	Required external PORESET duration minimum	16/F _{CLKIN}	clocks
2	Delay from PORESET deassertion to HRESET deassertion	521/F _{CLKIN}	clocks
Note:	Timings are not tested, but are guaranteed by design.		

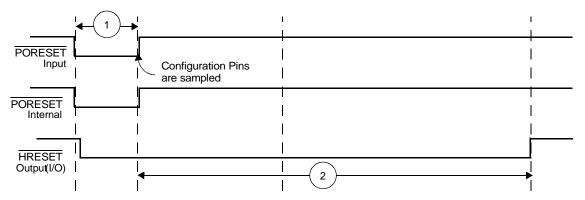


Figure 4. Timing Diagram for a Reset Configuration Write

MSC7119 Data Sheet, Rev. 8

Freescale Semiconductor

25



2.5.4 DDR DRAM Controller Timing

This section provides the AC electrical characteristics for the DDR DRAM interface.

2.5.4.1 DDR DRAM Input AC Timing Specifications

Table 17 provides the input AC timing specifications for the DDR DRAM interface.

Table 17. DDR DRAM Input AC Timing

No.	Parameter	Symbol	Min	Max	Unit
_	AC input low voltage	V _{IL}		V _{REF} - 0.31	V
_	AC input high voltage	V _{IH}	V _{REF} + 0.31	V _{DDM} + 0.3	V
201	Maximum Dn input setup skew relative to DQSn input	_	_	900	ps
202	Maximum Dn input hold skew relative to DQSn input	_	_	900	ps

Notes: 1. Maximum possible skew between a data strobe (DQSn) and any corresponding bit of data (D[8n + $\{0...7\}$] if $0 \le n \le 7$).

2. See Table 18 for t_{CK} value.

3. Dn should be driven at the same time as DQSn. This is necessary because the DQSn centering on the DQn data tenure is done internally.

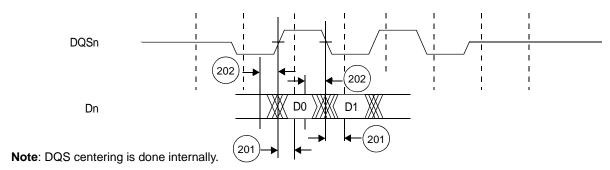


Figure 5. DDR DRAM Input Timing Diagram

2.5.4.2 DDR DRAM Output AC Timing Specifications

Table 18 and **Table 19** list the output AC timing specifications and measurement conditions for the DDR DRAM interface.

Table 18. DDR DRAM Output AC Timing

No.	Parameter	Symbol	Min	Max	Unit
200	CK cycle time, (CK/CK crossing) ¹ • 100 MHz (DDR200) • 150 MHz (DDR300)	t _{CK}	10 6.67		ns ns
204	An/RAS/CAS/WE/CKE output setup with respect to CK	t _{DDKHAS}	0.5 × t _{CK} – 1000	_	ps
205	An/RAS/CAS/WE/CKE output hold with respect to CK	t _{DDKHAX}	0.5 × t _{CK} – 1000	_	ps
206	CSn output setup with respect to CK	t _{DDKHCS}	0.5 × t _{CK} – 1000	_	ps
207	CSn output hold with respect to CK	t _{DDKHCX}	0.5 × t _{CK} – 1000		ps
208	CK to DQSn ²	t _{DDKHMH}	-600	600	ps



Table 18. DDR DRAM Output AC Timing (continued)

No.	Parameter	Symbol	Min	Max	Unit
209	Dn/DQMn output setup with respect to DQSn ³	t _{DDKHDS} , t _{DDKLDS}	0.25 × t _{CK} – 750	_	ps
210	Dn/DQMn output hold with respect to DQSn ³	t _{DDKHDX,} t _{DDKLDX}	0.25 × t _{CK} – 750	_	ps
211	DQSn preamble start ⁴	t _{DDKHMP}	$-0.25 \times t_{CK}$	_	ps
212	DQSn epilogue end ⁵	t _{DDKHME}	-600	600	ps

Notes:

- 1. All CK/CK referenced measurements are made from the crossing of the two signals ±0.1 V.
- 2. t_{DDKHMH} can be modified through the TCFG2[WRDD] DQSS override bits. The DRAM requires that the first write data strobe arrives 75–125% of a DRAM cycle after the write command is issued. Any skew between DQSn and CK must be considered when trying to achieve this 75%–125% goal. The TCFG2[WRDD] bits can be used to shift DQSn by 1/4 DRAM cycle increments. The skew in this case refers to an internal skew existing at the signal connections. By default, the CK/CK crossing occurs in the middle of the control signal (An/RAS/CAS/WE/CKE) tenure. Setting TCFG2[ACSM] bit shifts the control signal assertion 1/2 DRAM cycle earlier than the default timing. This means that the signal is asserted no earlier than 600 ps before the CK/CK crossing and no later than 600 ps after the crossing time; the device uses 1200 ps of the skew budget (the interval from –600 to +600 ps). Timing is verified by referencing the falling edge of CK. See Chapter 10 of the MSC711x Reference Manual for details.
- 3. Determined by maximum possible skew between a data strobe (DQS) and any corresponding bit of data. The data strobe should be centered inside of the data eye.
- 4. Please note that this spec is in reference to the DQSn first rising edge. It could also be referenced from CK(r), but due to programmable delay of the write strobes (TCFG2[WRDD]), there pre-amble may be extended for a full DRAM cycle. For this reason, we reference from DQSn.
- 5. All outputs are referenced to the rising edge of CK. Note that this is essentially the CK/DQSn skew in spec 208. In addition there is no real "maximum" time for the epilogue end. JEDEC does not require this is as a device limitation, but simply for the chip to guarantee fast enough write-to-read turn-around times. This is already guaranteed by the memory controller operation.

Figure 6 shows the DDR DRAM output timing diagram.

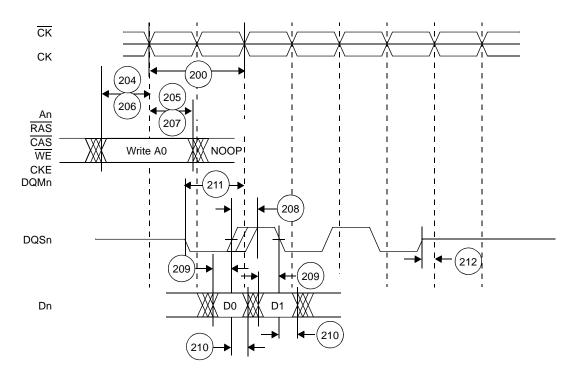


Figure 6. DDR DRAM Output Timing Diagram

Figure 7 provides the AC test load for the DDR DRAM bus.

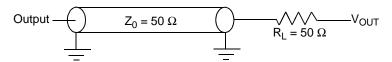


Figure 7. DDR DRAM AC Test Load

Table 19. DDR DRAM Measurement Conditions

		Symbol	DDR DRAM	Unit
V _{TH} ¹			V _{REF} ± 0.31 V	V
V _{OUT} ²			$0.5 \times V_{DDM}$	V
Notes:	1. 2.	Data input threshold measurement point. Data output measurement point.		

2.5.5 TDM Timing

Table 20. TDM Timing

No.	Characteristic	Expression	Min	Max	Units
300	TDMxRCK/TDMxTCK	TC	20.0	_	ns
301	TDMxRCK/TDMxTCK High Pulse Width	0.4 × TC	8.0	_	ns
302	TDMxRCK/TDMxTCK Low Pulse Width	0.4 × TC	8.0	_	ns
303	TDM all input Setup time		3.0	_	ns
304	TDMxRD Hold time		3.5	_	ns
305	TDMxTFS/TDMxRFS input Hold time		2.0	_	ns
306	TDMxTCK High to TDMxTD output active		4.0	_	ns
307	TDMxTCK High to TDMxTD output valid		_	14.0	ns
308	TDMxTD hold time		2.0	_	ns
309	TDMxTCK High to TDMxTD output high impedance		_	10.0	ns
310	TDMxTFS/TDMxRFS output valid		_	13.5	ns
311	TDMxTFS/TDMxRFS output hold time		2.5	_	ns

Notes: 1. Output values are based on 30 pF capacitive load.

^{2.} Inputs are referenced to the sampling that the TDM is programmed to use. Outputs are referenced to the programming edge they are programmed to use. Use of the rising edge or falling edge as a reference is programmable. Refer to the MSC711x Reference Manual for details. TDMxTCK and TDMxRCK are shown using the rising edge.

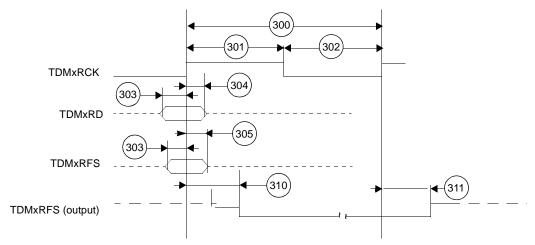


Figure 8. TDM Receive Signals

MSC7119 Data Sheet, Rev. 8



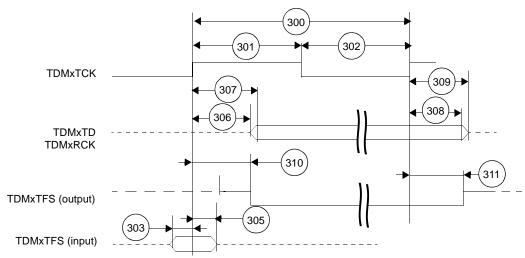


Figure 9. TDM Transmit Signals

2.5.6 Ethernet Timing

2.5.6.1 Receive Signal Timing

Table 21. Receive Signal Timing

No.	Characteristics	Min	Max	Unit
800	Receive clock period:			
	• MII: RXCLK (max frequency = 25 MHz)	40	_	ns
	• RMII: REFCLK (max frequency = 50 MHz)	20	_	ns
801	Receive clock pulse width high—as a percent of clock period	35	65	%
	• MII: RXCLK	14	_	ns
	• RMII: REFCLK	7	_	ns
802	Receive clock pulse width low—as a percent of clock period:	35	65	%
	• MII: RXCLK	14	_	ns
	• RMII: REFCLK	7	_	ns
803	RXDn, RX_DV, CRS_DV, RX_ER to receive clock rising edge setup time	4	_	ns
804	Receive clock rising edge to RXDn, RX_DV, CRS_DV, RX_ER hold time	2	_	ns

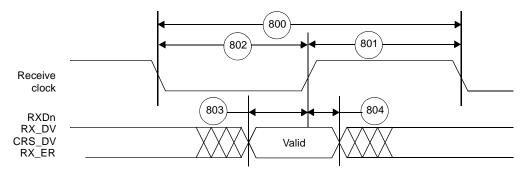


Figure 10. Ethernet Receive Signal Timing

2.5.6.2 Transmit Signal Timing

Table 22. Transmit Signal Timing

No.	Characteristics	Min	Max	Unit
800	Transmit clock period: • MII: TXCLK • RMII: REFCLK	40 20	_	ns ns
801	Transmit clock pulse width high—as a percent of clock period • MII: RXCLK • RMII: REFCLK	35 14 7	65 — —	% ns ns
802	Transmit clock pulse width low—as a percent of clock period: • MII: RXCLK • RMII: REFCLK	35 14 7	65 — —	% ns ns
805	Transmit clock to TXDn, TX_EN, TX_ER invalid	4	_	ns
806	Transmit clock to TXDn, TX_EN, TX_ER valid	_	14	ns

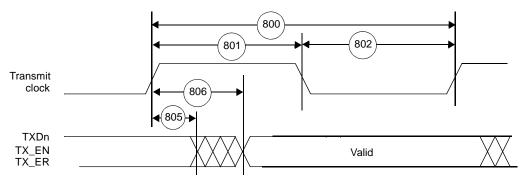


Figure 11. Ethernet Receive Signal Timing

2.5.6.3 Asynchronous Input Signal Timing

Table 23. Asynchronous Input Signal Timing

No.	Characteristics	Min	Max	Unit
807	MII: CRS and COL minimum pulse width (1.5 × TXCLK period) RMII: CRS_DV minimum pulse width (1.5 x REFCLK period)	60 30	_	ns ns



Figure 12. Asynchronous Input Signal Timing



2.5.6.4 Management Interface Timing

Table 24. Ethernet Controller Management Interface Timing

No.	Characteristics	Min	Max	Unit
808	MDC period	400	_	ns
809	MDC pulse width high	160	_	ns
810	MDC pulse width low	160	_	ns
811	MDS falling edge to MDIO output invalid (minimum propagation delay)	0	_	ns
812	MDS falling edge to MDIO output valid (maximum propagation delay)	_	15	ns
813	MDIO input to MDC rising edge setup time	10	_	ns
814	MDC rising edge to MDIO input hold time	10	_	ns

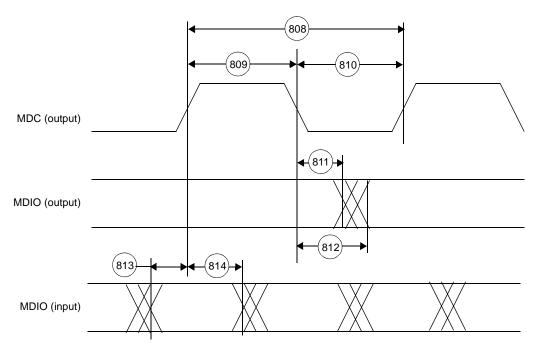


Figure 13. Serial Management Channel Timing



2.5.7 HDI16 Signals

Table 25. Host Interface (HDI16) Timing^{1, 2}

No.	Characteristics ³	Expression	Value	Unit
40	Host Interface Clock period	T _{CORE}	Note 1	ns
44a	Read data strobe minimum assertion width ⁴ HACK read minimum assertion width	2.0 × T _{CORE} + 9.0	Note 11	ns
44b	Read data strobe minimum deassertion width ⁴ HACK read minimum deassertion width	1.5 × T _{CORE}	Note 11	ns
44c	Read data strobe minimum deassertion width ⁴ after "Last Data Register" reads ^{5,6} , or between two consecutive CVR, ICR, or ISR reads ⁷ HACK minimum deassertion width after "Last Data Register" reads ^{5,6}	2.5 × T _{CORE}	Note 11	ns
45	Write data strobe minimum assertion width ⁸ HACK write minimum assertion width	1.5 × T _{CORE}	Note 11	ns
46	Write data strobe minimum deassertion width HACK write minimum deassertion width after ICR, CVR and Data Register writes ⁵	2.5 × T _{CORE}	Note 11	ns
47	Host data input minimum setup time before write data strobe deassertion Host data input minimum setup time before HACK write deassertion	_	2.5	ns
48	Host data input minimum hold time after write data strobe deassertion Host data input minimum hold time after HACK write deassertion	_	2.5	ns
49	Read data strobe minimum assertion to output data active from high impedance ⁴ HACK read minimum assertion to output data active from high impedance	_	1.0	ns
50	Read data strobe maximum assertion to output data valid ⁴ HACK read maximum assertion to output data valid	(2.0 × T _{CORE}) + 8.0	Note 11	ns
51	Read data strobe maximum deassertion to output data high impedance HACK read maximum deassertion to output data high impedance	_	9.0	ns
52	Output data minimum hold time after read data strobe deassertion ⁴ Output data minimum hold time after HACK read deassertion	_	1.0	ns
53	HCS[1–2] minimum assertion to read data strobe assertion ⁴	_	0.5	ns
54	HCS[1–2] minimum assertion to write data strobe assertion ⁸	_	0.0	ns
55	HCS[1–2] maximum assertion to output data valid	$(2.0 \times T_{CORE}) + 6.0$	Note 11	ns
56	HCS[1–2] minimum hold time after data strobe deassertion ⁹	_	0.5	ns
57	HA[0–2], HRW minimum setup time before data strobe assertion ⁹	_	5.0	ns
58	HA[0–2], HRW minimum hold time after data strobe deassertion ⁹	_	5.0	ns
61	Maximum delay from read data strobe deassertion to host request deassertion for "Last Data Register" read ^{4, 5, 10}	$(3.0 \times T_{CORE}) + 6.0$	Note 11	ns
62	Maximum delay from write data strobe deassertion to host request deassertion for "Last Data Register" write ^{5,8,10}	(3.0 × T _{CORE}) + 6.0	Note 11	ns
63	Minimum delay from DMA HACK (OAD=0) or Read/Write data strobe(OAD=1) deassertion to HREQ assertion.	(2.0 × T _{CORE}) + 1.0	Note 11	ns
64	Maximum delay from DMA HACK (OAD=0) or Read/Write data strobe(OAD=1) assertion to HREQ deassertion	(5.0 × T _{CORE}) + 6.0	Note 11	ns

Notes:

- 1. T_{CORE} = core clock period. At 300 MHz, T_{CORE} = 3.333 ns.
- 2. In the timing diagrams below, the controls pins are drawn as active low. The pin polarity is programmable.
- 3. $V_{DD} = 3.3 \text{ V} \pm 0.15 \text{ V}$; $T_{J} = -40 ^{\circ}\text{C}$ to +105 $^{\circ}\text{C}$, $C_{L} = 30 \text{ pF}$ for maximum delay timings and $C_{L} = 0 \text{ pF}$ for minimum delay timings.
- 4. The read data strobe is $\overline{\text{HRD}}/\text{HRD}$ in the dual data strobe mode and $\overline{\text{HDS}}/\text{HDS}$ in the single data strobe mode.
- 5. For 64-bit transfers, the "last data register" is the register at address 0x7, which is the last location to be read or written in data transfers. This is RX0/TX0 in the little endian mode (HBE = 0), or RX3/TX3 in the big endian mode (HBE = 1).
- 6. This timing is applicable only if a read from the "last data register" is followed by a read from the RX[0–3] registers without first polling RXDF or HREQ bits, or waiting for the assertion of the HREQ/HREQ signal.
- 7. This timing is applicable only if two consecutive reads from one of these registers are executed.
- 8. The write data strobe is HWR in the dual data strobe mode and HDS in the single data strobe mode.
- 9. The data strobe is host read (HRD/HRD) or host write (HWR/HWR) in the dual data strobe mode and host data strobe (HDS/HDS) in the single data strobe mode.
- 10. The host request is HREQ/HREQ in the single host request mode and HRRQ/HRRQ and HTRQ/HTRQ in the double host request mode. HRRQ/HRRQ is deasserted only when HOTX fifo is empty, HTRQ/HTRQ is deasserted only if HORX fifo is full
- 11. Compute the value using the expression.
- 12. The read and write data strobe minimum deassertion width for non-"last data register" accesses in single and dual data strobe modes is based on timings 57 and 58.



Figure 14 and Figure 15 show HDI16 read signal timing. Figure 16 and Figure 17 show HDI16 write signal timing.

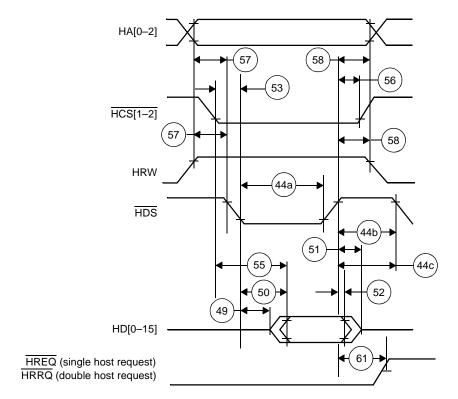


Figure 14. Read Timing Diagram, Single Data Strobe

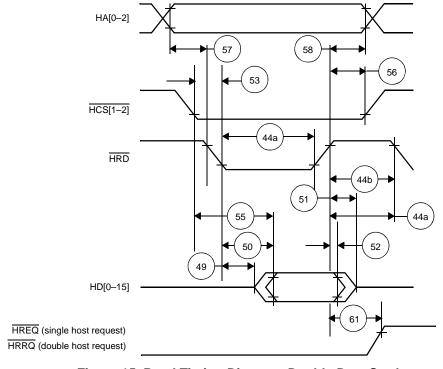


Figure 15. Read Timing Diagram, Double Data Strobe



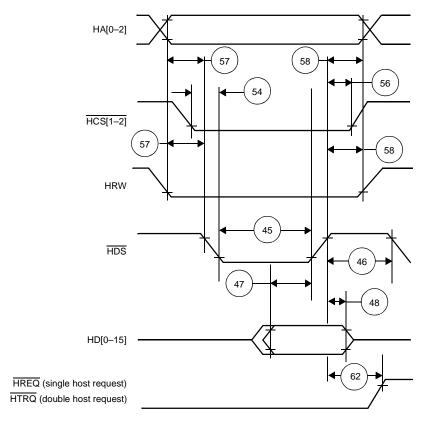


Figure 16. Write Timing Diagram, Single Data Strobe

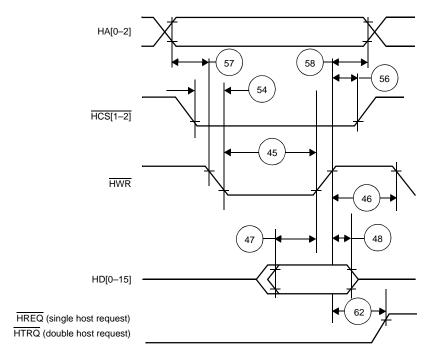


Figure 17. Write Timing Diagram, Double Data Strobe



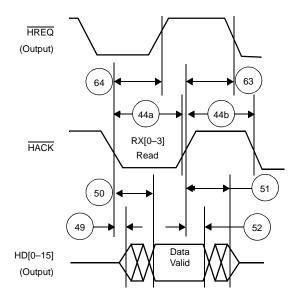


Figure 18. Host DMA Read Timing Diagram, HPCR[OAD] = 0

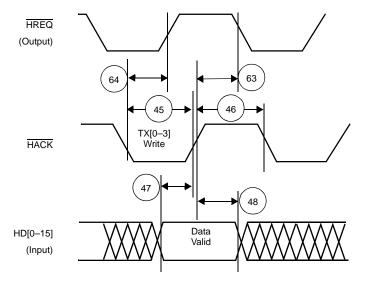


Figure 19. Host DMA Write Timing Diagram, HPCR[OAD] = 0



I²C Timing 2.5.8

Table 26. I²C Timing

No.	Ch avantariatia	Fast		Unit	
	Characteristic	Min	Max		
450	SCL clock frequency	0	400	kHz	
451	Hold time START condition	(SCL clock period/2) – 0.3	_	μs	
452	SCL low period	(SCL clock period/2) – 0.3	_	μs	
453	SCL high period	(SCL clock period/2) – 0.1	_	μs	
454	Repeated START set-up time (not shown in figure)	2 × 1/F _{BCK}	_	μs	
455	Data hold time	0	_	μs	
456	Data set-up time	250	_	ns	
457	SDA and SCL rise time	_	700	ns	
458	SDA and SCL fall time	_	300	ns	
459	Set-up time for STOP	(SCL clock period/2) – 0.7	_	μs	
460	Bus free time between STOP and START	(SCL clock period/2) – 0.3	_	μs	
Note:	SDA set-up time is referenced to the rising edge of SCL. SDA hold time is referenced to the falling edge of SCL. Load capacitance on SDA and SCL is 400 pF.				

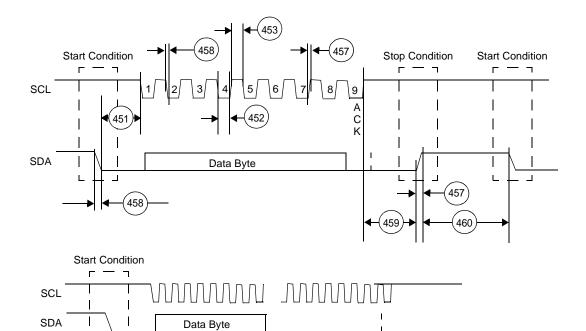


Figure 20. I²C Timing Diagram



UART Timing 2.5.9

Table 27. UART Timing

No.	Characteristics	Expression	Min	Max	Unit
_	Internal bus clock (APBCLK)	F _{CORE} /2	_	150	MHz
_	Internal bus clock period (1/APBCLK)	T _{APBCLK}	6.67	_	ns
400	URXD and UTXD inputs high/low duration	16×T _{APBCLK}	106.67	_	ns
401	URXD and UTXD inputs rise/fall time		_	5	ns
402	UTXD output rise/fall time		_	5	ns

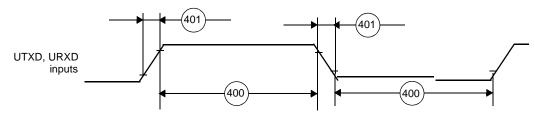


Figure 21. UART Input Timing

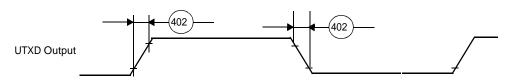


Figure 22. UART Output Timing

2.5.10 **EE Timing**

Table 28. EE0 Timing

Number	Characteristics	Туре	Min		
65 EE0 input to the core		Asynchronous	4 core clock periods		
66 EE0 output from the core		Synchronous to core clock	1 core clock period		
Notes: 1 The core clock is the SC1400 core clock. The ratio between the core clock and CLKOLIT is configured during newer on recet					

- Configure the direction of the EE pin in the EE_CTRL register (see the SC140/SC1400 Core Reference Manual for details.

 - Refer to Table 1-11 on page 1-16 for details on EE pin functionality.

Figure 24 shows the signal behavior of the EE pin.

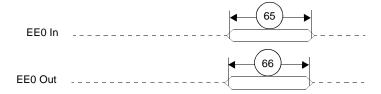


Figure 23. EE Pin Timing



2.5.11 Event Timing

Table 29. EVNT Signal Timing

Number		Characteristics	Туре	Min				
67 EVNT as input		EVNT as input	Asynchronous	1.5 × APBCLK periods				
68 EVNT as output		EVNT as output	Synchronous to core clock	1 APBCLK period				
Notes: 1. Refer to Table 27 for a definition of the APBCLK period.								
2.	. Dire	Direction of the EVNT signal is configured through the GPIO and Event port registers.						
3.	. Ref	fer to the signal chapter in the MSC711x	Reference Manual for details on EVNT pir	Refer to the signal chapter in the MSC711x Reference Manual for details on EVNT pin functionality.				

Figure 24 shows the signal behavior of the EVNT pins.

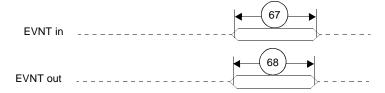


Figure 24. EVNT Pin Timing

2.5.12 GPIO Timing

Table 30. GPIO Signal Timing 1,2,3

Number	Characteristics Type		Min
601	GPI ^{4.5}	Asynchronous	1.5 × APBCLK periods
602	GPO ⁵	Synchronous to core clock	1 APBCLK period
603	Port A edge-sensitive interrupt	Asynchronous	1.5 × APBCLK periods
604	Port A level-sensitive interrupt	Asynchronous	3 × APBCLK periods ⁶

Notes: 1. Refer to Table 27 for a definition of the APBCLK period.

- 2. Direction of the GPIO signal is configured through the GPIO port registers.
- 3. Refer to Section 1.5 for details on GPIO pin functionality.
- 4. GPI data is synchronized to the APBCLK internally and the minimum listed is the capability of the hardware to capture data into a register when the GPADR is read. The specification is not tested due to the asynchronous nature of the input and dependence on the state of the DSP core. It is guaranteed by design.
- 5. The output signals cannot toggle faster than 75 MHz.
- Level-sensitive interrupts should be held low until the system determines (via the service routine) that the interrupt is acknowledged.

Figure 25 shows the signal behavior of the GPI/GPO pins.

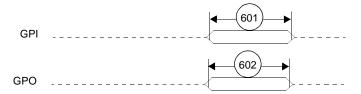


Figure 25. GPI/GPO Pin Timing



2.5.13 JTAG Signals

Table 31. JTAG Timing

N.	Characteristics	All fred	Juencies	l lmit		
No.	Characteristics	Min	Max	Unit		
700	TCK frequency of operation $(1/(T_C \times 3))$ Note: $T_C = 1/\text{CLOCK}$ which is the period of the core clock. The TCK frequency must less than 1/3 of the core frequency with an absolute maximum limit of 40 MHz.	0.0	40.0	MHz		
701	TCK cycle time	25.0	_	ns		
702	TCK clock pulse width measured at V _{M =} 1.6 V	11.0	_	ns		
703	TCK rise and fall times	0.0	3.0	ns		
704	Boundary scan input data set-up time	5.0	_	ns		
705	Boundary scan input data hold time	14.0	_	ns		
706	TCK low to output data valid	0.0	20.0	ns		
707	TCK low to output high impedance	0.0	20.0	ns		
708	TMS, TDI data set-up time	5.0	_	ns		
709	TMS, TDI data hold time	14.0	_	ns		
710	TCK low to TDO data valid	0.0	24.0	ns		
711	TCK low to TDO high impedance	0.0	10.0	ns		
712	TRST assert time 100.0 — ns					
Note:	All timings apply to OCE module data transfers as the OCE module uses the JTAG port as an interface.					

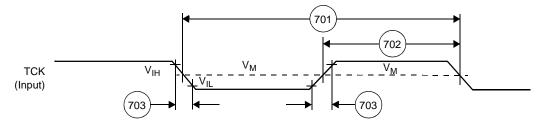


Figure 26. Test Clock Input Timing Diagram



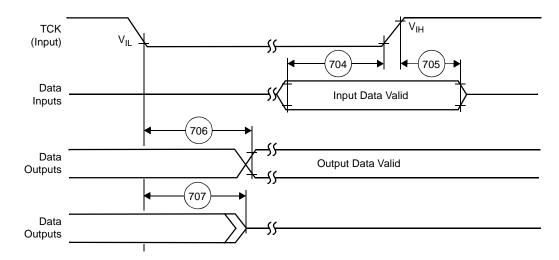


Figure 27. Boundary Scan (JTAG) Timing Diagram

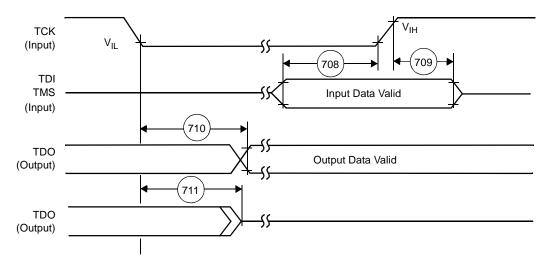


Figure 28. Test Access Port Timing Diagram



Figure 29. TRST Timing Diagram



3 Hardware Design Considerations

This section described various areas to consider when incorporating the MSC7119 device into a system design.

3.1 Thermal Design Considerations

An estimation of the chip-junction temperature, T_J, in °C can be obtained from the following:

$$T_J = T_A + (R_{\Theta JA} \times P_D)$$
 Eqn. 1

where

 T_A = ambient temperature near the package (°C)

 R_{AIA} = junction-to-ambient thermal resistance (°C/W)

 $P_D = P_{INT} + P_{I/O} = power dissipation in the package (W)$

 $P_{INT} = I_{DD} \times V_{DD} = internal power dissipation (W)$

 $P_{I/O}$ = power dissipated from device on output pins (W)

The power dissipation values for the MSC7119 are listed in **Table 4**. The ambient temperature for the device is the air temperature in the immediate vicinity that would cool the device. The junction-to-ambient thermal resistances are JEDEC standard values that provide a quick and easy estimation of thermal performance. There are two values in common usage: the value determined on a single layer board and the value obtained on a board with two planes. The value that more closely approximates a specific application depends on the power dissipated by other components on the printed circuit board (PCB). The value obtained using a single layer board is appropriate for tightly packed PCB configurations. The value obtained using a board with internal planes is more appropriate for boards with low power dissipation (less than 0.02 W/cm² with natural convection) and well separated components. Based on an estimation of junction temperature using this technique, determine whether a more detailed thermal analysis is required. Standard thermal management techniques can be used to maintain the device thermal junction temperature below its maximum. If T_J appears to be too high, either lower the ambient temperature or the power dissipation of the chip.

You can verify the junction temperature by measuring the case temperature using a small diameter thermocouple (40 gauge is recommended) or an infrared temperature sensor on a spot on the device case. Use the following equation to determine T_I:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$
 Eqn. 2

where

 T_T = thermocouple (or infrared) temperature on top of the package (°C)

 Ψ_{JT} = thermal characterization parameter (°C/W)

 P_D = power dissipation in the package (W)

3.2 Power Supply Design Considerations

This section outlines the MSC7119 power considerations: power supply, power sequencing, power planes, decoupling, power supply filtering, and power consumption. It also presents a recommended power supply design and options for low-power consumption. For information on AC/DC electrical specifications and thermal characteristics, refer to **Section 2**.

3.2.1 Power Supply

The MSC7119 requires four input voltages, as shown in **Table 32**.

Table 32. MSC7119 Voltages

Voltage	Symbol	Value
Core	V _{DDC}	1.2 V
Memory	V_{DDM}	2.5 V
Reference	V _{REF}	1.25 V
I/O	V _{DDIO}	3.3 V

You should supply the MSC7119 core voltage via a variable switching supply or regulator to allow for compatibility with possible core voltage changes on future silicon revisions. The core voltage is supplied with 1.2 V (+5% and -10%) across V_{DDC} and GND and the I/O section is supplied with 3.3 V (±10%) across V_{DDIO} and GND. The memory and reference voltages supply the DDR memory controller block. The memory voltage is supplied with 2.5 V across V_{DDM} and GND. The reference voltage is supplied across V_{REF} and GND and must be between $0.49 \times V_{DDM}$ and $0.51 \times V_{DDM}$. Refer to the JEDEC standard JESD8 (Stub Series Terminated Logic for 2.5 Volts (STTL_2)) for memory voltage supply requirements.

3.2.2 Power Sequencing

One consequence of multiple power supplies is that the voltage rails ramp up at different rates when power is initially applied. The rates depend on the power supply, the type of load on each power supply, and the way different voltages are derived. It is extremely important to observe the power up and power down sequences at the board level to avoid latch-up, forward biasing of ESD devices, and excessive currents, which all lead to severe device damage.

Note: There are five possible power-up/power-down sequence cases. The first four cases listed in the following sections are recommended for new designs. The fifth case is not recommended for new designs and must be carefully evaluated for current spike risks based on actual information for the specific application.



3.2.2.1 Case 1

The power-up sequence is as follows:

- 1. Turn on the V_{DDIO} (3.3 V) supply first.
- 2. Turn on the V_{DDC} (1.2 V) supply second.
- 3. Turn on the V_{DDM} (2.5 V) supply third.
- 4. Turn on the V_{REF} (1.25 V) supply fourth (last).

The power-down sequence is as follows:

- 1. Turn off the V_{REF} (1.25 V) supply first.
- 2. Turn off the V_{DDM} (2.5 V) supply second.
- 3. Turn off the V_{DDC} (1.2 V) supply third.
- 4. Turn of the V_{DDIO} (3.3 V) supply fourth (last).

Use the following guidelines:

- Make sure that the time interval between the ramp-down of V_{DDIO} and V_{DDC} is less than 10 ms.
- Make sure that the time interval between the ramp-up or ramp-down for V_{DDC} and V_{DDM} is less than 10 ms for power-up and power-down.
- Refer to **Figure 30** for relative timing for power sequencing case 1.

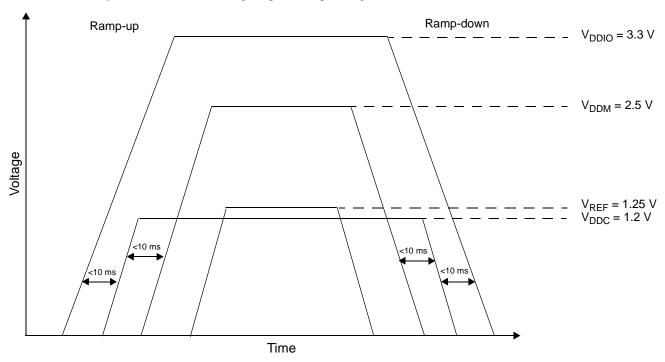


Figure 30. Voltage Sequencing Case 1



3.2.2.2 Case 2

The power-up sequence is as follows:

- 1. Turn on the V_{DDIO} (3.3 V) supply first.
- 2. Turn on the V_{DDC} (1.2 V) and V_{DDM} (2.5 V) supplies simultaneously (second).
- 3. Turn on the V_{REF} (1.25 V) supply last (third).

Note: Make sure that the time interval between the ramp-up of V_{DDIO} and V_{DDC}/V_{DDM} is less than 10 ms.

The power-down sequence is as follows:

- 1. Turn off the V_{REF} (1.25 V) supply first.
- 2. Turn off the V_{DDM} (2.5 V) supply second.
- 3. Turn off the V_{DDC} (1.2 V) supply third.
- 4. Turn of the V_{DDIO} (3.3 V) supply fourth (last).

Use the following guidelines:

- Make sure that the time interval between the ramp-down for V_{DDIO} and V_{DDC} is less than 10 ms.
- Make sure that the time interval between the ramp-up or ramp-down for V_{DDC} and V_{DDM} is less than 10 ms for power-up and power-down.
- Refer to **Figure 31** for relative timing for Case 2.

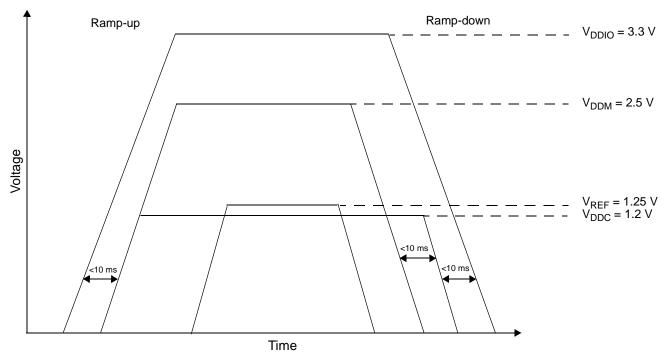


Figure 31. Voltage Sequencing Case 2

45



3.2.2.3 Case 3

The power-up sequence is as follows:

- 1. Turn on the V_{DDIO} (3.3 V) supply first.
- 2. Turn on the V_{DDC} (1.2 V) supply second.
- 3. Turn on the V_{DDM} (2.5 V) and V_{REF} (1.25 V) supplies simultaneously (third).

Note: Make sure that the time interval between the ramp-up of V_{DDIO} and V_{DDC} is less than 10 ms.

The power-down sequence is as follows:

- 1. Turn off the V_{DDM} (2.5 V) and V_{REF} (1.25 V) supplies simultaneously (first).
- 2. Turn off the V_{DDC} (1.2 V) supply second.
- 3. Turn of the V_{DDIO} (3.3 V) supply third (last).

Use the following guidelines:

- Make sure that the time interval between the ramp-down for V_{DDIO} and V_{DDC} is less than 10 ms.
- Make sure that the time interval between the ramp-up or ramp-down time for V_{DDC} and V_{DDM} is less than 10 ms for power-up and power-down.
- Refer to **Figure 32** for relative timing for Case 3.

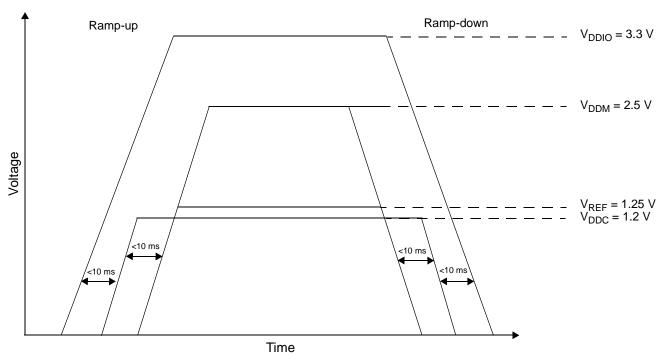


Figure 32. Voltage Sequencing Case 3

MSC7119 Data Sheet, Rev. 8



3.2.2.4 Case 4

The power-up sequence is as follows:

- 1. Turn on the V_{DDIO} (3.3 V) supply first.
- 2. Turn on the V_{DDC} (1.2 V), V_{DDM} (2.5 V), and V_{REF} (1.25 V) supplies simultaneously (second).

Note: Make sure that the time interval between the ramp-up of V_{DDIO} and V_{DDC} is less than 10 ms.

The power-down sequence is as follows:

- 1. Turn off the V_{DDC} (1.2 V), V_{REF} (1.25 V), and V_{DDM} (2.5 V) supplies simultaneously (first).
- 2. Turn of the V_{DDIO} (3.3 V) supply last.

Use the following guidelines:

- Make sure that the time interval between the ramp-up or ramp-down time for V_{DDC} and V_{DDM} is less than 10 ms for power-up and power-down.
- Refer to **Figure 33** for relative timing for Case 4.

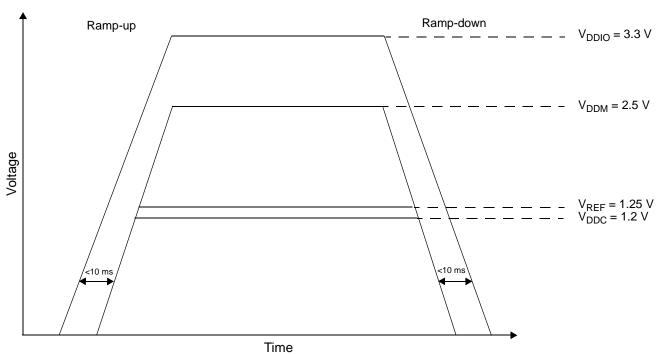


Figure 33. Voltage Sequencing Case 4



3.2.2.5 Case 5 (not recommended for new designs)

The power-up sequence is as follows:

- 1. Turn on the V_{DDIO} (3.3 V) supply first.
- 2. Turn on the V_{DDM} (2.5 V) supply second.
- 3. Turn on the V_{DDC} (1.2 V) supply third.
- 4. Turn on the V_{REF} (1.25 V) supply fourth (last).

Note: Make sure that the time interval between the ramp-up of V_{DDIO} and V_{DDM} is less than 10 ms.

The power-down sequence is as follows:

- 1. Turn off the V_{REF} (1.25 V) supply first.
- 2. Turn off the V_{DDC} (1.2 V) supply second.
- 3. Turn off the V_{DDM} (2.5 V) supply third.
- 4. Turn of the V_{DDIO} (3.3 V) supply fourth (last).

Use the following guidelines:

- Make sure that the time interval between the ramp-down of V_{DDIO} and V_{DDM} is less than 10 ms.
- Make sure that the time interval between the ramp-up or ramp-down for V_{DDC} and V_{DDM} is less than 2 ms for power-up and power-down.
- Refer to **Figure 34** for relative timing for power sequencing case 5.

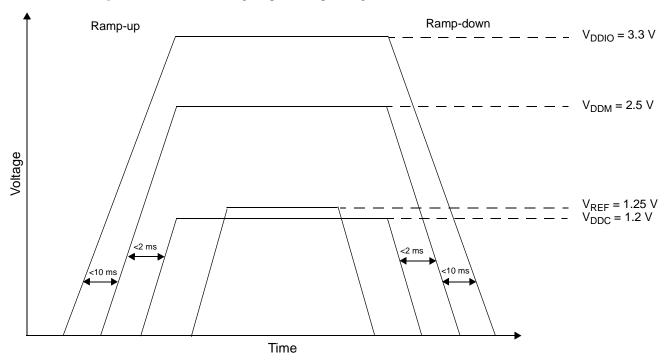


Figure 34. Voltage Sequencing Case 5

Note: Cases 1, 2, 3, and 4 are recommended for system design. Designs that use Case 5 may have large current spikes on the V_{DDM} supply at startup and is not recommended for most designs. If a design uses case 5, it must accommodate the potential current spikes. Verify risks related to current spikes using actual information for the specific application.

MSC7119 Data Sheet, Rev. 8

Freescale Semiconductor

47

3.2.3 Power Planes

Each power supply pin (V_{DDC} , V_{DDM} , and V_{DDO}) should have a low-impedance path to the board power supply. Each GND pin should be provided with a low-impedance path to ground. The power supply pins drive distinct groups of logic on the device. The MSC7119 V_{DDC} power supply pins should be bypassed to ground using decoupling capacitors. The capacitor leads and associated printed circuit traces connecting to device power pins and GND should be kept to less than half an inch per capacitor lead. A minimum four-layer board that employs two inner layers as power and GND planes is recommended. See **Section 3.5** for DDR Controller power guidelines.

3.2.4 Decoupling

Both the I/O voltage and core voltage should be decoupled for switching noise. For I/O decoupling, use standard capacitor values of $0.01~\mu F$ for every two to three voltage pins. For core voltage decoupling, use two levels of decoupling. The first level should consist of a $0.01~\mu F$ high frequency capacitor with low effective series resistance (ESR) and effective series inductance (ESL) for every two to three voltage pins. The second decoupling level should consist of two bulk/tantalum decoupling capacitors, one $10~\mu F$ and one $47~\mu F$, (with low ESR and ESL) mounted as closely as possible to the MSC7119 voltage pins. Additionally, the maximum drop between the power supply and the DSP device should be 15~mV at 1~A.

3.2.5 PLL Power Supply Filtering

The MSC7119 V_{DDPLL} power signal provides power to the clock generation PLL. To ensure stability of the internal clock, the power supplied to this pin should be filtered with capacitors that have low and high frequency filtering characteristics. V_{DDPLL} can be connected to V_{DDC} through a 2 Ω resistor. V_{SSPLL} can be tied directly to the GND plane. A circuit similar to the one shown in **Figure 35** is recommended. The PLL loop filter should be placed as closely as possible to the V_{DDPLL} pin (which are located on the outside edge of the silicon package) to minimize noise coupled from nearby circuits. The 0.01 μ F capacitor should be closest to V_{DDPLL} , followed by the 0.1 μ F capacitor, the 10 μ F capacitor, and finally the 2- Ω resistor to V_{DDC} . These traces should be kept short.

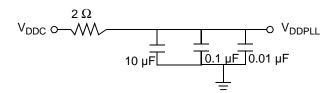


Figure 35. PLL Power Supply Filter Circuits

3.2.6 Power Consumption

You can reduce power consumption in your design by controlling the power consumption of the following regions of the device:

- Extended core. Use the SC1400 Stop and Wait modes by issuing a stop or wait instruction.
- Clock synthesis module. Disable the PLL, timer, watchdog, or DDR clocks or disable the CLKO pin.
- AHB subsystem. Freeze or shut down the AHB subsystem using the GPSCTL[XBR HRQ] bit.
- Peripheral subsystem. Halt the individual on-device peripherals such as the DDR memory controller, Ethernet MAC, HDI16, TDM, UART, I²C, and timer modules.

For details, see the "Clocks and Power Management" chapter of the MSC711x Reference Manual.



3.2.7 Power Supply Design

One of the most common ways to derive power is to use either a simple fixed or adjustable linear regulator. For the system I/O voltage supply, a simple fixed 3.3 V supply can be used. However, a separate adjustable linear regulator supply for the core voltage V_{DDC} should be implemented. For the memory power supply, regulators are available that take care of all DDR power requirements.

Table 33. Recommended Power Supply Ratings

Supply	Symbol	Nominal Voltage	Current Rating
Core	V _{DDC}	1.2 V	1.5 A per device
Memory	V_{DDM}	2.5 V	0.5 A per device
Reference	V _{REF}	1.25 V	10 μA per device
I/O	V _{DDIO}	3.3 V	1.0 A per device

3.3 Estimated Power Usage Calculations

The following equations permit estimated power usage to be calculated for individual design conditions. Overall power is derived by totaling the power used by each of the major subsystems:

$$P_{TOTAL} = P_{CORE} + P_{PERIPHERALS} + P_{DDRIO} + P_{IO} + P_{LEAKAGE}$$
 Eqn. 3

This equation combines dynamic and static power. Dynamic power is determined using the generic equation:

$$C \times V^2 \times F \times 10^{-3} \text{ mW}$$
 Eqn. 4

where,

C = load capacitance in pF

V = peak-to-peak voltage swing in V

F = frequency in MHz

3.3.1 Core Power

Estimation of core power is straightforward. It uses the generic dynamic power equation and assumes that the core load capacitance is 750 pF, core voltage swing is 1.2 V, and the core frequency is 300 MHz. This yields:

$$P_{CORF} = 750 \text{ pF} \times (1.2 \text{ V})^2 \times 300 \text{ MHz} \times 10^{-3} = 324.0 \text{ mW}$$
 Eqn. 5

This equation allows for adjustments to voltage and frequency if necessary.

3.3.2 Peripheral Power

Peripherals include the DDR memory controller, Ethernet controller, DMA controller, HDI16, TDM, UART, timers, GPIOs, and the I²C module. Basic power consumption by each module is assumed to be the same and is computed by using the following equation which assumes an effective load of 20 pF, core voltage swing of 1.2 V, and a switching frequency of 100 MHz. This yields:

$$P_{PERIPHERAL} = 20 \text{ pF} \times (1.2 \text{ V})^2 \times 150 \text{ MHz} \times 10^{-3} = 4.32 \text{ mW per peripheral}$$
 Eqn. 6

Multiply this value by the number of peripherals used in the application to compute the total peripheral power consumption.

3.3.3 External Memory Power

Estimation of power consumption by the DDR memory system is complex. It varies based on overall system signal line usage, termination and load levels, and switching rates. Because the DDR memory includes terminations external to the MSC7119 device, the 2.5 V power source provides the power for the termination, which is a static value of 16 mA per signal driven high. The dynamic power is computed, however, using a differential voltage swing of $\pm 0.200 \text{ V}$, yielding a peak-to-peak swing of 0.4 V. The equations for computing the DDR power are:

$$P_{DDRIO} = P_{STATIC} + P_{DYNAMIC}$$
 Eqn. 7

$$P_{STATIC} = (unused pins \times \% driven high) \times 16 \text{ mA} \times 2.5 \text{ V}$$
 Eqn. 8

$$P_{DYNAMIC} = (pin \ activity \ value) \times 20 \ pF \times (0.4 \ V)^2 \times 300 \ MHz \times 10^{-3} \ mW$$
 Eqn. 9

pin activity value = (active data lines \times % activity \times % data switching) + (active address lines \times % activity) Eqn. 10

As an example, assume the following:

unused pins = 16 (DDR uses 16-pin mode)

% driven high = 50%

active data lines = 16

% activity = 60%

% data switching = 50%

active address lines = 3

In this example, the DDR memory power consumption is:

$$P_{DDRIO} = ((16 \times 0.5) \times 16 \times 2.5) + (((16 \times 0.6 \times 0.5) + (3 \times 0.6)) \times 20 \times (0.4)^{2} \times 300 \times 10^{-3}) = 326.3 \text{ mW}$$
 Eqn. 11

3.3.4 External I/O Power

The estimation of the I/O power is similar to the computation of the peripheral power estimates. The power consumption per signal line is computed assuming a maximum load of 20 pF, a voltage swing of 3.3 V, and a switching frequency of 25 MHz, which yields:

$$P_{IO} = 20 \text{ pF} \times (3.3 \text{ V})^2 \times 25 \text{ MHz} \times 10^{-3} = 5.44 \text{ mW per I/O line}$$
 Eqn. 12

Multiply this number by the number of I/O signal lines used in the application design to compute the total I/O power.

Note: The signal loading depends on the board routing. For systems using a single DDR device, the load could be as low as 7 pF.

3.3.5 Leakage Power

The leakage power is for all power supplies combined at a specific temperature. The value is temperature dependent. The observed leakage value at room temperature is 64 mW.

MSC7119 Data Sheet, Rev. 8



3.3.6 Example Total Power Consumption

Using the examples in this section and assuming four peripherals and 10 I/O lines active, a total power consumption value is estimated as the following:

$$P_{TOTAL} = 324.0 + (4 \times 4.32) + 326.3 + (10 \times 5.44) + 64 = 784.98 \text{ mW}$$
 Eqn. 13

3.4 Reset and Boot

This section describes the recommendations for configuring the MSC7119 at reset and boot.

3.4.1 Reset Circuit

 $\overline{\text{HRESET}}$ is a bidirectional signal and, if driven as an input, should be driven with an open collector or open-drain device. For an open-drain output such as $\overline{\text{HRESET}}$, take care when driving many buffers that implement input bus-hold circuitry. The bus-hold currents can cause enough voltage drop across the pull-up resistor to change the logic level to low. Either a smaller value of pull-up or less current loading from the bus-hold drivers overcomes this issue. To avoid exceeding the MSC7119 output current, the pull-up value should not be too small (a 1 K Ω pull-up resistor is used in the MSC711xADS reference design).

3.4.2 Reset Configuration Pins

Table 34 shows the MSC7119 reset configuration signals. These signals are sampled at the deassertion (rising edge) of PORESET. For details, refer to the Reset chapter of the MSC711x Reference Manual.

Signal	Description	Settings	
BM[3-0]	Determines boot mode.	See Table 35 for details.	
SWTE	Determines watchdog functionality.	0 Watchdog timer disabled.	
		1 Watchdog timer enabled.	
HDSP	Configures HDI16 strobe polarity.	0 Host Data strobes active low.	
		1 Host Data strobes active high.	
H8BIT	Configures HDI16 operation mode.	0 HDI16 port configured for 16-bit operation.	
		1 HDI16 port configured for 8-bit operation.	

Table 34. Reset Configuration Signals



Table 35. Boot Mode Source Selection

BM[3-0]	Boot Port	Input Clock Frequency	Clock Divide	PLL	CKSEL	RNG Bit	Core Clock Frequency	Comments
HDI Boot Mo	odes							•
0000	HDI16	< F _{max}	N/A	N/A	00	0	< F _{max}	Not clocked by the PLL. Can boot as 8- or 16-bit HDI.
0101	HDI16	22.2-25 MHz	1	12	11	1	266-300 MHz	Can boot as 8- or 16-bit HDI.
0010	HDI16	25-33.3 MHz	2	32	01	1	200-266 MHz	1
0111	HDI16	33-66 MHz	3	12	11	1	132-264 MHz	1
0100	HDI16	44.3-50 MHz	2	12	11	1	266-300 MHz	1
SPI Boot Mo	odes - Using H	A3, HCS2, BM3, I	BM2 Pins		•			
1000	SPI (SW)	< F _{max}	N/A	N/A	00	0	< F _{max}	The boot program automatically
1001	SPI (SW)	15.6-25 MHz	1	17	11	0	133–212.5 MHz	determines whether EEPROM
1010	SPI (SW)	33-50 MHz	2	16	11	0	132–200 MHz	or Flash memory.
1011	SPI (SW)	44.3-75 MHz	3	18	11	0	133–225 MHz	1
SPI Boot Mo	odes - Using U	RXD, UTXD, SCL	, SDA Pins		•			
1100	SPI (SW)	< F _{max}	N/A	N/A	00	0	< F _{max}	Boots through different set of pins.
I ² C Boot Mo	des	Į.						1 -
0001	l ² C	< 100 MHz	N/A	N/A	00	0	< 100 MHz	Not clocked by the PLL. I ² C is limited to a maximum bit rate of 400 Kbps. With a clock divider of 128, this limits the maximum input clock frequency to 100 MHz.
Reserved								•
0011	Reserved	_	_	_	_	_	_	_
0110	Reserved	_	_	_	_	_	_	_
1101	Reserved	_	_	_	_	_	_	_
1110	Reserved	_	_		_	_	_	_
1111	Reserved							

- F_{max} is determined by the maximum frequency of the peripheral and of the SC1400 core as specified in the data sheet.

3.4.3 **Boot**

After a power-on reset, the PLL is bypassed and the device is directly clocked from the CLKIN pin. Thus, the device operates slowly during the boot process. After the boot program is loaded, it can enable the PLL and start the device operating at a higher speed. The MSC7119 can boot from an external host through the HDI16 or download a user program through the I²C port. The boot operating mode is set by configuring the BM[0-3] signals sampled at the rising edge of PORESET, as shown in Table 35. See the MSC711x Reference Manual for details of boot program operation.

3.4.3.1 **HDI16 Boot**

If the MSC7119 device boots from an external host through the HDI16, the port is configured as follows:

- Operate in Non-DMA mode.
- Operate in polled mode on the device side.
- Operate in polled mode on the external host side.
- External host must write four 16-bit values at a time with the first word as the most significant and the fourth word as the least significant.



When booting from a power-on reset, the HDI16 is additionally configurable as follows:

- 8- or 16-bit mode as specified by the H8BIT pin.
- Data strobe as specified by the HDSP and HDDS pins.

These pins are sampled only on the deassertion of power-on reset. During a boot from a hard reset, the configuration of these pins is unaffected.

Note: When the HDI16 is used for booting or other purposes, bit 0 is the least significant bit and not the most significant bit as for other DSP products.

3.4.3.2 I²C Boot

When the MSC7119 device is configured to boot from the I^2C port, the boot program configures the GPIO pins for I^2C operation. Then the MSC7118 device initiates accesses to the I^2C module, downloading data to the MSC7118 device. The I^2C interface is configured as follows:

- PLL is disabled and bypassed so that the I²C module is clocked with the IPBus clock.
- I²C interface operates in master mode and polling is used.
- EPROM operates in slave mode.
- Clock divider is set to 128.
- Address of slave during boot is 0xA0.

The IPBus clock is internally divided to generate the bit clock, as follows:

- CLKIN must be a maximum of 100 MHz
- PLL is bypassed.
- IPBus clock = CLKIN/2 is a maximum of 50 MHz.
- I²C bit clock must be less than or equal to:
 - IPBus clock/I²C clock divider
 - 50 MHz (max)/128
 - 390.6 KHz

This satisfies the maximum clock rate requirement of 400 kbps for the I²C interface. For details on the boot procedure, see the "Boot Program" chapter of the MSC711x Reference Manual.

3.4.3.3 SPI Boot

When the MSC7119 device is configured to boot from the SPI port, the boot program configures the GPIO pins for SPI operation. Then the MSC7118 device initiates accesses to the SPI module, downloading data to the MSC7118 device. When the SPI routines run in the boot ROM, the MSC7118 is always configured as the SPI master. Booting through the SPI is supported for serial EEPROM devices and serial Flash devices. When a READ_ID instruction is issued to the serial memory device and the device returns a value of 0x00 or 0xFF, the routines for accessing a serial EEPROM are used, at a maximum frequency of 4 Mbps. Otherwise, the routines for accessing a serial Flash are used, and they can run at faster speeds. Booting is performed through one of two sets of pins:

- Main set: BM[2–3], HA3, and HCS2, which allow use of the PLL.
- Alternate set: UTXD, URXD, SDA, and SCL, which cannot be used with the PLL.

In either configuration, an error during SPI boot is flagged on the EVNT3 pin. For details on the boot procedure, see the "Boot Program" chapter of the *MSC711x Reference Manual*.



3.5 DDR Memory System Guidelines

MSC7119 devices contain a memory controller that provides a glueless interface to external double data rate (DDR) SDRAM memory modules with Class 2 Series Stub Termination Logic 2.5 V (SSTL_2). There are two termination techniques, as shown in Figure 36. Technique B is the most popular termination technique.

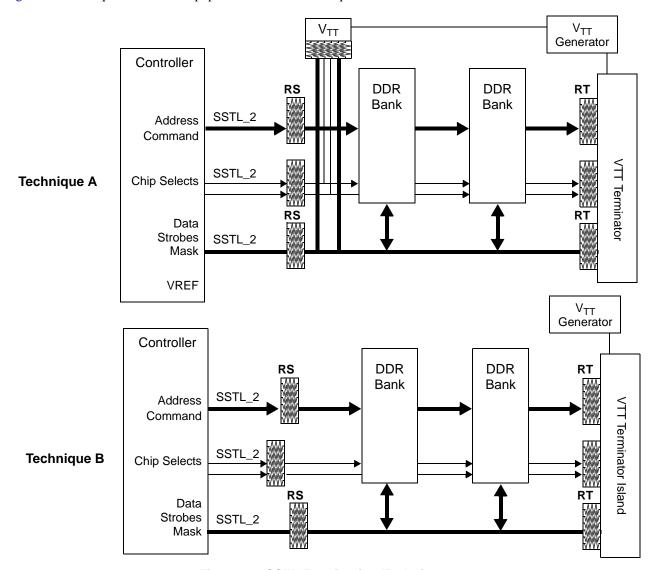


Figure 36. SSTL Termination Techniques

Figure 37 illustrates the power wattage for the resistors. Typical values for the resistors are as follows:

- $RS = 22 \Omega$
- $RT = 24 \Omega$



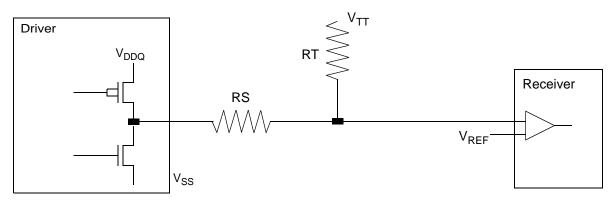


Figure 37. SSTL Power Value

3.5.1 V_{REF} and V_{TT} Design Constraints

 V_{TT} and V_{REF} are isolated power supplies at the same voltage, with V_{TT} as a high current power source. This section outlines the voltage supply design needs and goals:

- Minimize the noise on both rails.
- V_{TT} must track variation in the V_{REF} DC offsets. Although they are isolated supplies, one possible solution is to use a single IC to generate both signals.
- Both references should have minimal drift over temperature and source supply.
- It is important to minimize the noise from coupling onto V_{REF} as follows:
 - Isolate V_{REF} and shield it with a ground trace.
 - Use 15–20 mm track.
 - Use 20–30 mm clearance between other traces for isolating.
 - Use the outer layer route when possible.
 - Use distributed decoupling to localize transient currents and return path and decouple with an inductance less than 3 nH.
- Max source/sink transient currents of up to 1.8 A for a 32-bit data bus.
- Use a wide island trace on the outer layer:
 - Place the island at the end of the bus.
 - Decouple both ends of the bus.
 - Use distributed decoupling across the island.
 - Place SSTL termination resistors inside the V_{TT} island and ensure a good, solid connection.
- Place the V_{TT} regulator as closely as possible to the termination island.
 - Reduce inductance and return path.
 - Tie current sense pin at the midpoint of the island.

3.5.2 Decoupling

The DDR decoupling considerations are as follows:

- DDR memory requires significantly more burst current than previous SDRAMs.
- In the worst case, up to 64 drivers may be switching states.
- Pay special attention and decouple discrete ICs per manufacturer guidelines.
- Leverage V_{TT} island topology to minimize the number of capacitors required to supply the burst current needs of the termination rail.
- See the Micron DesignLine publication entitled *Decoupling Capacitor Calculation for a DDR Memory Channel* (http://download.micron.com/pdf/pubs/designline/3Q00dl1-4.pdf).

3.5.3 General Routing

The general routing considerations for the DDR are as follows:

- All DDR signals must be routed next to a solid reference:
 - For data, next to solid ground planes.
 - For address/command, power planes if necessary.
- All DDR signals must be impedance controlled. This is system dependent, but typical values are 50–60 ohm.
- Minimize other cross-talk opportunities. As possible, maintain at least a four times the trace width spacing between all DDR signals to non-DDR signals.
- Keep the number of vias to a minimum to eliminate additional stubs and capacitance.
- Signal group routing priorities are as follows:
 - DDR clocks.
 - Route MVTT/MVREF.
 - Data group.
 - Command/address.
- Minimize data bit jitter by trace matching.

3.5.4 Routing Clock Distribution

The DDR clock distribution considerations are as follows:

- DDR controller supports six clock pairs:
 - 2 DIMM modules.
 - Up to 36 discrete chips.
- For route traces as for any other differential signals:
 - Maintain proper difference pair spacing.
 - Match pair traces within 25 mm.
- Match all clock traces to within 100 mm.
- Keep all clocks equally loaded in the system.
- Route clocks on inner critical layers.

3.5.5 Data Routing

The DDR data routing considerations are as follows:

- Route each data group (8-bits data + DQS + DM) on the same layer. Avoid switching layers within a byte group.
- Take care to match trace lengths, which is extremely important.
- To make trace matching easier, let adjacent groups be routed on alternate critical layers.
- Pin swap bits within a byte group to facilitate routing (discrete case).
- Tight trace matching is recommended within the DDR data group. Keep each 8-bit datum and its DM signal within ± 25 mm of its respective strobe.
- Minimize lengths across the entire DDR channel:
 - Between all groups maintain a delta of no more than 500 mm.
 - Allows greater flexibility in the design for readjustments as needed.
- DDR data group separation:
 - If stack-up allows, keep DDR data groups away from the address and control nets.
 - Route address and control on separate critical layers.
 - If resistor networks (RNs) are used, attempt to keep data and command lines in separate packages.



3.6 Connectivity Guidelines

This section summarizes the connections and special conditions, such as pull-up or pull-down resistors, for the MSC7119 device. Following are guidelines for signal groups and configuration settings:

- Clock and reset signals.
 - SWTE is used to configure the MSC7119 device and is sampled on the deassertion of PORESET, so it should be tied to V_{DDC} or GND either directly or through pull-up or pull-down resistors until PORESET is deasserted. After PORESET, this signal can be left floating.
 - BM[0-1] configure the MSC7119 device and are sampled until PORESET is deasserted, so they should be tied to V_{DDIO} or GND either directly or through pull-up or pull-down resistors.
 - HRESET should be pulled up.
- Interrupt signals. When used, \overline{IRQ} pins must be pulled up.
- HDI16 signals.
 - When they are configured for open-drain, the HREQ/HREQ or HTRQ/HTRQ signals require a pull-up resistor. However, these pins are also sampled at power-on reset to determine the HDI16 boot mode and may need to be pulled down. When these pins must be pulled down on reset and pulled up otherwise, a buffer can be used with the HRESET signal as the enable.
 - When the device boots through the HDI16, the HDDS, HDSP and H8BIT pins should be pulled up or down, depending on the required boot mode settings.
- Ethernet MAC/TDM2 signals. The MDIO signal requires an external pull-up resistor.
- I^2C signals. The SCL and SDA signals, when programmed for I^2C , requires an external pull-up resistor.
- General-purpose I/O (GPIO) signals. An unused GPIO pin can be disconnected. After boot, program it as an output pin.
- Other signals.
 - The $\overline{\mathsf{TEST0}}$ pin must be connected to ground.
 - The TPSEL pin should be pulled up to enable debug access via the EOnCE port and pulled down for boundary scan.
 - Pins labelled NO CONNECT (NC) must not be connected.
 - When a 16-pin double data rate (DDR) interface is used, the 16 unused data pins should be no connects (floating) if the used lines are terminated.
 - Do not connect DBREQ to DONE (as you would for the MSC8101 device). Connect DONE to one of the EVNT pins, and DBREQ to HRRQ.

4 Ordering Information

Consult a Freescale Semiconductor sales office or authorized distributor to determine product availability and place an order.

Part	Supply Voltage	Package Type	Pin Count	Core Frequency (MHz)	Solder Spheres	Order Number
MSC7119	1.2 V core 2.5 V memory	Molded Array Process-Ball Grid Array (MAP-BGA)	400	300	Lead-free	MSC7119VM1200
	3.3 V I/O	Allay (MATE BOTT)			Lead-bearing	MSC7119VF1200

5 Package Information

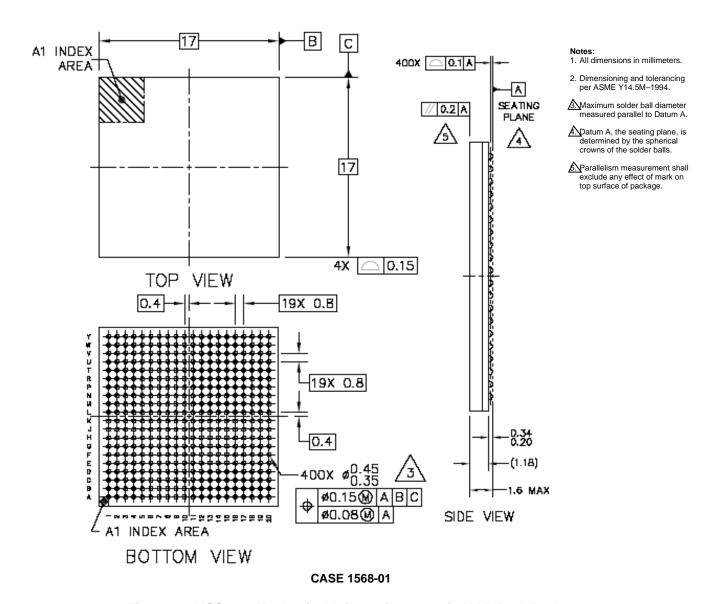


Figure 38. MSC7119 Mechanical Information, 400-pin MAP-BGA Package

6 Product Documentation

- *MSC711x Reference Manual* (MSC711xRM). Includes functional descriptions of the extended cores and all the internal subsystems including configuration and programming information.
- Application Notes. Cover various programming topics related to the StarCore DSP core and the MSC7119 device.
- *SC140/SC1400 DSP Core Reference Manual*. Covers the SC140 and SC1400 core architecture, control registers, clock registers, program control, and instruction set.



7 Revision History

Table 36 provides a revision history for this data sheet.

Table 36. Document Revision History

Revision	Date	Description
0	Sep. 2005	Initial public release.
1	Oct 2005	Added explanatory note to HDI16 timing table.
2	Oct. 2005	 Added information about signals GPIOB11, GPIOC11, GPIOD7, and GPIOD8 to the signal descriptions and pinout location lists.
3	Dec. 2005	Added information about signals GPIOA16, GPIOA17, GPIOA27, GPIOA28, and GPIOA29 to signal description and pinout location lists.
4	Feb. 2006	Updated orderable part numbers.
5	Nov. 2006	 Updated Reference Manual reference to MSC711x Reference Manual. Updated arrows in Host DMA Writing Timing figure.
6	Jun. 2007	 Updated to new data sheet format. Reorganized and renumbered sections, figures, and tables. Added a note to clarify the definition of TCK timing 700 in new Table 31. Removed references to V_{CCSYN} and V_{CCSYN1} in the new power supply design recommendation Section 3.2.
7	Aug 2007	• The power-up and power-down sequences described in Section 3.2 starting on page 42 have been expanded to five possible design scenarios/cases. These cases replace the previously recommended power-up/power-down sequence recommendations. Section 3.2 has been clarified by adding subsection headings.
8	Apr 2008	• Change the PLL filter resistor from 20 Ω to 2 Ω in Section 3.2.5.



How to Reach Us:

Home Page:

www.freescale.com

Web Support:

http://www.freescale.com/support

USA/Europe or Locations Not Listed:

Freescale Semiconductor, Inc.
Technical Information Center, EL516
2100 East Elliot Road
Tempe, Arizona 85284
+1-800-521-6274 or
+1-480-768-2130
www.freescale.com/support

Europe, Middle East, and Africa:

Freescale Halbleiter Deutschland GmbH Technical Information Center Schatzbogen 7 81829 Muenchen, Germany +44 1296 380 456 (English) +46 8 52200080 (English) +49 89 92103 559 (German) +33 1 69 35 48 48 (French)

Japan:

Freescale Semiconductor Japan Ltd. Headquarters
ARCO Tower 15F
1-8-1, Shimo-Meguro, Meguro-ku
Tokyo 153-0064
Japan
0120 191014 or
+81 3 5437 9125
support.japan@freescale.com

www.freescale.com/support

Asia/Pacific:

Freescale Semiconductor Hong Kong Ltd.
Technical Information Center
2 Dai King Street
Tai Po Industrial Estate
Tai Po, N.T., Hong Kong
+800 2666 8080
support.asia@freescale.com

For Literature Requests Only:

Freescale Semiconductor
Literature Distribution Center
P.O. Box 5405
Denver, Colorado 80217
+1-800 441-2447 or
+1-303-675-2140
Fax: +1-303-675-2150
LDCForFreescaleSemiconductor
@hibbertgroup.com

Document Number: MSC7119

Rev. 8 4/2008 Information in this document is provided solely to enable system and software implementers to use Freescale Semiconductor products. There are no express or implied copyright licenses granted hereunder to design or fabricate any integrated circuits or integrated circuits based on the information in this document.

Freescale Semiconductor reserves the right to make changes without further notice to any products herein. Freescale Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Freescale Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters that may be provided in Freescale Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals", must be validated for each customer application by customer's technical experts. Freescale Semiconductor does not convey any license under its patent rights nor the rights of others. Freescale Semiconductor products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Freescale Semiconductor product could create a situation where personal injury or death may occur. Should Buyer purchase or use Freescale Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold Freescale Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Freescale Semiconductor was negligent regarding the design or manufacture of the part.

RoHS-compliant and/or Pb-free versions of Freescale products have the functionality and electrical characteristics as their non-RoHS-compliant and/or non-Pb-free counterparts. For further information, see http://www.freescale.com or contact your Freescale sales representative.

For information on Freescale's Environmental Products program, go to http://www.freescale.com/epp.

Freescale[™], the Freescale logo, CodeWarrior, fieldBIST, and StarCore are trademarks of Freescale Semiconductor, Inc. IEEE, 802.3, 802.3u, 802.3x, and 802.3ac are trademarks of the Institute of Electrical and Electronics Engineers, Inc. (IEEE). All other product or service names are the property of their respective owners.

© Freescale Semiconductor, Inc. 2004, 2008. All rights reserved.



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Digital Signal Processors & Controllers - DSP, DSC category:

Click to view products by NXP manufacturer:

Other Similar products are found below:

ADSP-2189NBCAZ-320 ADSP-BF703BBCZ-3 dsPIC33EV64GM002-ISP DSPIC33FJ128MC510-I/PF MWPR1516CFM ADSP-2185MKCAZ-300 ADSP-BF701KBCZ-1 dsPIC33EV128GM002-ISP 646890G ADSP-21587KBCZ-4B ADSP-BF701KBCZ-2 ADSP-SC582KBCZ-4A ADSP-SC584KBCZ-3A ADSP-SC589KBCZ-4B ADSP-SC583KBCZ-4A ADSP-BF703BBCZ-4 DSP-BF705KBCZ-4 ADSP-BF705BBCZ-3 DSPIC33FJ64GP708-IPT ADBF707WCBCZ411 ADBF706WCCPZ411 ADSP-21584KBCZ-4A MC56F82746VLFR ADBF704WCCPZ311 ADBF702WCCPZ411 AD21571WCSWZ400 MC56F84550VLFR ADSP-SC571CSWZ-5 ADBF700WCCPZ211 ADSC572WCBCZ302 ADSC572WCBCZ402 ADSC572WCBCZ4202 AD21489WBCPZ402 ADSC572WCBCZ4200 ADSC572WCBCZ4200 ADSC571WCSWZ300 ADSC571WCSWZ500 ADSC571WCSWZ500 ADSC571WCSWZ300 ADSC571WCSWZ500 ADSC571WCSWZ300 ADSC571WCSWZ500 ADSC571WCSWZ300 ADSC571WCSWZ500 ADSC571WCSWZ500 ADSC571WCSWZ300 ADSC571WCSWZ300 ADSC571WCSWZ500 ADSC571WCSWZ500 ADSC571WCSWZ300 ADSC571WCSWZ500 ADSC571WCSWZ500 ADSC571WCSWZ300 ADSC571WCSWZ500 ADSC571WCS